



# LOW-NOISE, HIGH-SPEED, CURRENT FEEDBACK AMPLIFIERS

Check for Samples: [THS3112](#), [THS3115](#)

## FEATURES

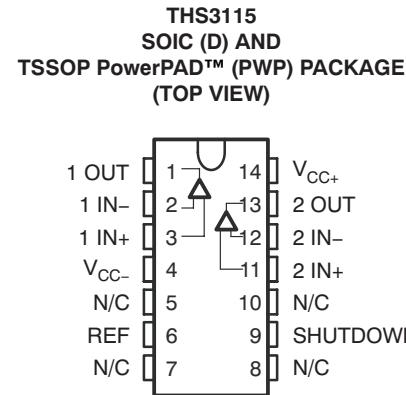
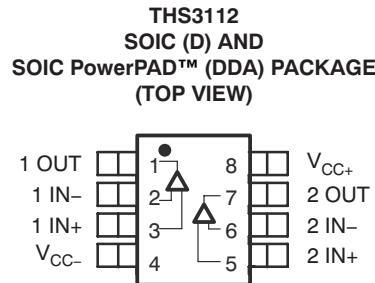
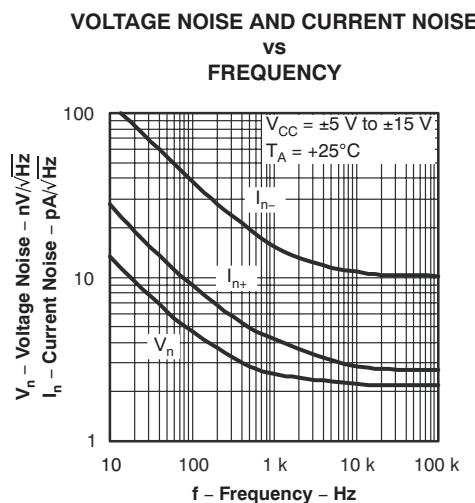
- **Low Noise:**
  - $2.9\text{-pA}/\sqrt{\text{Hz}}$  Noninverting Current Noise
  - $10.8\text{-pA}/\sqrt{\text{Hz}}$  Inverting Current Noise
  - $2.2\text{-nV}/\sqrt{\text{Hz}}$  Voltage Noise
- **Wide Supply Voltage Range:**  $\pm 5\text{ V}$  to  $\pm 15\text{ V}$
- **Wide Output Swing:**
  - $25\text{-V}_{\text{PP}}$  Output Voltage,  $R_{\text{L}} = 100\text{ }\Omega$ ,  $\pm 15\text{-V}$  Supply
- **High Output Current:**  $150\text{ mA}$  (Min)
- **High Speed:**
  - $110\text{-MHz}$  ( $-3\text{-dB}$  BW,  $G = 1$ ,  $\pm 15\text{ V}$ )
  - $1550\text{-V}/\mu\text{s}$  Slew Rate ( $G = 2$ ,  $\pm 15\text{ V}$ )
- **Low Distortion ( $G = 2$ ):**
  - $-78\text{ dBc}$  (1 MHz,  $2\text{ V}_{\text{PP}}$ ,  $100\text{-}\Omega$  Load)
- **Low-Power Shutdown (THS3115)**
  - $300\text{-}\mu\text{A}$  Shutdown Quiescent Current per Channel
- **Standard SOIC, SOIC PowerPAD™, and TSSOP PowerPAD Packages**
- **Evaluation Module Available**

## APPLICATIONS

- Communication Equipment
- Video Distribution
- Motor Drivers
- Piezo Drivers

## DESCRIPTION

The THS3112/5 are low-noise, high-speed current feedback amplifiers, ideal for any application requiring high output current. The low noninverting current noise of  $2.9\text{ pA}/\sqrt{\text{Hz}}$  and the low inverting current noise of  $10.8\text{ pA}/\sqrt{\text{Hz}}$  increase signal-to-noise ratios for enhanced signal resolution. The THS3112/5 can operate from  $\pm 5\text{-V}$  to  $\pm 15\text{-V}$  supply voltages, while drawing as little as  $4.5\text{ mA}$  of supply current per channel. It offers low  $-78\text{-dBc}$  total harmonic distortion driving  $2\text{ V}_{\text{PP}}$  into a  $100\text{-}\Omega$  load. The THS3115 features a low-power shutdown mode, consuming only  $300\text{-}\mu\text{A}$  shutdown quiescent current per channel. The THS3112/5 are packaged in standard SOIC, SOIC PowerPAD™, and TSSOP PowerPAD packages.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

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 This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

 ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

### AVAILABLE OPTIONS<sup>(1)</sup>

T <sub>A</sub>	PACKAGED DEVICE				EVALUATION MODULES
	SOIC-8 (D)	SOIC-8 PowerPAD (DDA)	SOIC-14 (D)	TSSOP-14 (PWP)	
0°C to +70°C	THS3112CD	THS3112CDDA	THS3115CD	THS3115CPWP	THS3112EVM THS3115EVM
40°C to +85°C	THS3112ID	THS3112IDDA	THS3115ID	THS3115IPWP	

(1) For the most current specification and package information, refer to the Package Option Addendum located at the end of this data sheet or see the TI web site at [www.ti.com](http://www.ti.com).

### ABSOLUTE MAXIMUM RATINGS<sup>(1)</sup>

Over operating free-air temperature (unless otherwise noted).

		UNIT
Supply voltage, V <sub>CC+</sub> to V <sub>CC-</sub>		33 V
Input voltage		±V <sub>CC</sub>
Output current (see <sup>(2)</sup> )		275 mA
Differential input voltage		±4 V
Maximum junction temperature		+150°C
Total power dissipation at (or below) +25°C free-air temperature		See Dissipation Ratings Table
Operating free-air temperature, T <sub>A</sub>	Commercial	0°C to +70°C
	Industrial	-40°C to +85°C
Storage temperature, T <sub>stg</sub>	Commercial	-65°C to +125°C
	Industrial	-65°C to +125°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) The THS3122 and THS3125 may incorporate a PowerPAD™ on the underside of the chip. This pad acts as a heatsink and must be connected to a thermally dissipating plane for proper power dissipation. Failure to do so may result in exceeding the maximum junction temperature which could permanently damage the device. See TI Technical Brief [SLMA002](http://www.ti.com/lit/tech/slma002) for more information about utilizing the PowerPAD™ thermally-enhanced package.

### DISSIPATION RATINGS TABLE

PACKAGE	θ <sub>JA</sub>	T <sub>A</sub> = +25°C POWER RATING
D-8	95°C/W <sup>(1)</sup>	1.32 W
DDA	67°C/W	1.87 W
D-14	66.6°C/W <sup>(1)</sup>	1.88 W
PWP	37.5°C/W	3.3 W

(1) These data were taken using the JEDEC proposed high-K test PCB. For the JEDEC low-K test PCB, the θ<sub>JA</sub> is 168°C/W for the D-8 package and 122.3°C/W for the D-14 package.

## RECOMMENDED OPERATING CONDITIONS

		MIN	NOM	MAX	UNIT
Supply voltage, $V_{CC+}$ to $V_{CC-}$	Dual supply	$\pm 5$	$\pm 15$		V
	Single supply	10	30		
Operating free-air temperature, $T_A$	C-suffix	0	+70		°C
	I-suffix	-40	+85		

## ELECTRICAL CHARACTERISTICS

Over operating free-air temperature range,  $T_A = +25^\circ\text{C}$ ,  $V_{CC} = \pm 15 \text{ V}$ ,  $R_F = 750 \Omega$ , and  $R_L = 100 \Omega$  (unless otherwise noted).

DYNAMIC PERFORMANCE		TEST CONDITIONS			MIN	TYP	MAX	UNIT
BW	Small-signal bandwidth (-3 dB)	$R_L = 100\Omega$	$R_F = 1 \text{ k}\Omega$ , $G = 1$	$V_{CC} = \pm 5 \text{ V}$	95			MHz
		$R_L = 100 \Omega$	$R_F = 750 \Omega$ , $G = 2$	$V_{CC} = \pm 5 \text{ V}$	103			
				$V_{CC} = \pm 15 \text{ V}$	110			
	Bandwidth (0.1 dB)	$R_F = 750 \Omega$ , $G = 2$		$V_{CC} = \pm 5 \text{ V}$	25			
				$V_{CC} = \pm 15 \text{ V}$	48			
SR	Slew rate <sup>(1)</sup> , $G = 8$	$G = 2$ , $R_F = 680\Omega$	$V_O = 10 \text{ V}_{PP}$	$V_{CC} = \pm 15 \text{ V}$	1550			$\text{V}/\mu\text{s}$
			$V_O = 5 \text{ V}_{PP}$	$V_{CC} = \pm 5 \text{ V}$	820			
				$V_{CC} = \pm 15 \text{ V}$	1300			
$t_s$	Settling time to 0.1%	$G = -1$	$V_O = 2 \text{ V}_{PP}$	$V_{CC} = \pm 5 \text{ V}$	50			ns
			$V_O = 5 \text{ V}_{PP}$	$V_{CC} = \pm 15 \text{ V}$	63			

(1) Slew rate is defined from the 25% to the 75% output levels.

NOISE/DISTORTION PERFORMANCE		TEST CONDITIONS			MIN	TYP	MAX	UNIT		
THD	Total harmonic distortion	$G = 2$ , $R_F = 680 \Omega$ , $V_{CC} = \pm 15 \text{ V}$ , $f = 1 \text{ MHz}$	$V_{O(PP)} = 2 \text{ V}$		-78			dBc		
			$V_{O(PP)} = 8 \text{ V}$		-75					
		$G = 2$ , $R_F = 680 \Omega$ , $V_{CC} = \pm 5 \text{ V}$ , $f = 1 \text{ MHz}$	$V_{O(PP)} = 2 \text{ V}$		-76					
			$V_{O(PP)} = 6 \text{ V}$		-74					
$V_n$	Input voltage noise	$V_{CC} = \pm 5 \text{ V}$ , $\pm 15 \text{ V}$	$f = 10 \text{ kHz}$		2.2			$\text{nV}/\sqrt{\text{Hz}}$		
$I_n$	Input current noise	Noninverting Input	$V_{CC} = \pm 5 \text{ V}$ , $\pm 15 \text{ V}$	$f = 10 \text{ kHz}$	2.9			$\text{pA}/\sqrt{\text{Hz}}$		
		Inverting Input			10.8					
Crosstalk			$G = 2$ , $f = 1 \text{ MHz}$ , $V_O = 2 \text{ V}_{PP}$	$V_{CC} = \pm 5 \text{ V}$	-67			dBc		
				$V_{CC} = \pm 15 \text{ V}$	-67					
Differential gain error			$G = 2$ , $R_L = 150 \Omega$ 40 IRE modulation $\pm 100 \text{ IRE Ramp}$ NTSC and PAL	$V_{CC} = \pm 5 \text{ V}$	0.01			%		
				$V_{CC} = \pm 15 \text{ V}$	0.01					
Differential phase error				$V_{CC} = \pm 5 \text{ V}$	0.011			degrees		
				$V_{CC} = \pm 15 \text{ V}$	0.011					

**ELECTRICAL CHARACTERISTICS (continued)**Over operating free-air temperature range,  $T_A = +25^\circ\text{C}$ ,  $V_{CC} = \pm 15\text{ V}$ ,  $R_F = 750\text{ }\Omega$ , and  $R_L = 100\text{ }\Omega$  (unless otherwise noted).

DC PERFORMANCE		PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
$V_{IO}$	Input offset voltage	$V_{CC} = \pm 5\text{ V}, V_{CC} = \pm 15\text{ V}$	$T_A = +25^\circ\text{C}$	6	10		mV	
			$T_A = \text{full range}$		13			
			$T_A = +25^\circ\text{C}$	1	3		$\mu\text{V}/^\circ\text{C}$	
	Channel offset voltage matching		$T_A = \text{full range}$		4			
			$T_A = \text{full range}$	10				
$I_{IB}$	IN- Input bias current	$V_{CC} = \pm 5\text{ V}, V_{CC} = \pm 15\text{ V}$	$T_A = +25^\circ\text{C}$		23		$\mu\text{A}$	
			$T_A = \text{full range}$		30			
	IN+ Input bias current		$T_A = +25^\circ\text{C}$	0.33	2		$\mu\text{A}$	
			$T_A = \text{full range}$		3			
			$T_A = +25^\circ\text{C}$	4	22			
$I_{IO}$	Input offset current		$T_A = \text{full range}$		30		$\mu\text{A}$	
	Open-loop transimpedance		$R_L = 1\text{ k}\Omega$	1				

INPUT CHARACTERISTICS								
PARAMETER		TEST CONDITIONS			MIN	TYP	MAX	UNIT
$V_{ICR}$	Input common-mode voltage range	$V_{CC} = \pm 5\text{ V}$		$T_A = \text{full range}$	$\pm 2.5$	$\pm 2.7$		V
		$V_{CC} = \pm 15\text{ V}$			$\pm 12.5$	$\pm 12.7$		
CMRR	Common-mode rejection ratio	$V_{CC} = \pm 5\text{ V}$ , $V_I = -2.5\text{ V}$ to $2.5\text{ V}$		$T_A = +25^\circ\text{C}$	56	62		dB
				$T_A = \text{full range}$	54			
		$V_{CC} = \pm 15\text{ V}$ , $V_I = -12.5\text{ V}$ to $12.5\text{ V}$		$T_A = +25^\circ\text{C}$	63	67		
				$T_A = \text{full range}$	60			
$R_I$	Input resistance	IN+				1.5		$\text{M}\Omega$
		IN-				15		$\Omega$
$C_I$	Input capacitance					2		$\text{pF}$

OUTPUT CHARACTERISTICS								
PARAMETER		TEST CONDITIONS			MIN	TYP	MAX	UNIT
$V_O$	Output voltage swing	$G = 4, V_I = 1\text{ V}, V_{CC} = \pm 5\text{ V}$		$R_L = 1\text{ k}\Omega$	$T_A = +25^\circ\text{C}$	3.9		V
				$R_L = 100\Omega$	$T_A = +25^\circ\text{C}$	3.6	3.8	
		$G = 4, V_I = 3.4\text{ V}, V_{CC} = \pm 15\text{ V}$		$R_L = 1\text{ k}\Omega$	$T_A = \text{full range}$	3.4		V
				$R_L = 100\Omega$	$T_A = +25^\circ\text{C}$	13.5		
				$R_L = 100\Omega$	$T_A = +25^\circ\text{C}$	12.2	13.3	
$I_O$	Output current drive	$G = 4, V_I = 0.9\text{ V}, V_{CC} = \pm 5\text{ V}$		$R_L = 25\Omega$	$T_A = +25^\circ\text{C}$	100	130	$\text{mA}$
		$G = 4, V_I = 1.7\text{ V}, V_{CC} = \pm 15\text{ V}$		$R_L = 25\Omega$	$T_A = +25^\circ\text{C}$	175	270	$\text{mA}$
$r_o$	Output resistance	Open loop				14		$\Omega$

## ELECTRICAL CHARACTERISTICS (continued)

Over operating free-air temperature range,  $T_A = +25^\circ\text{C}$ ,  $V_{CC} = \pm 15\text{ V}$ ,  $R_F = 750\text{ }\Omega$ , and  $R_L = 100\text{ }\Omega$  (unless otherwise noted).

POWER SUPPLY		TEST CONDITIONS	MIN	TYP	MAX	UNIT
I <sub>CC</sub>	Quiescent current (per channel)		T <sub>A</sub> = +25°C	4.4	5.5	mA
	T <sub>A</sub> = full range		6			
PSRR	Power-supply rejection ratio	V <sub>CC</sub> = ±15 V	T <sub>A</sub> = +25°C	4.9	6.5	
			T <sub>A</sub> = full range		7.5	
		V <sub>CC</sub> = ±5 V	T <sub>A</sub> = +25°C	53	60	dB
			T <sub>A</sub> = full range	50		
I <sub>CC</sub>	Shutdown quiescent current (per channel)	V <sub>CC</sub> = ±15 V	T <sub>A</sub> = +25°C	60	69	
			T <sub>A</sub> = full range	55		

### SHUTDOWN CHARACTERISTICS (THS3115 Only)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
V <sub>REF</sub>	REF pin voltage level		V <sub>CC</sub> –		V <sub>CC</sub> – – 4	V
V <sub>SHDN</sub>	SHUTDOWN pin voltage level	Enable			REF + 0.8	V
		Disable		REF + 2		V
I <sub>CC(SHDN)</sub>	Shutdown quiescent current (per channel)	REF = 0 V, V <sub>CC</sub> = ±5 V to ±15 V		0.3	0.45	mA
t <sub>DIS</sub>	Disable time <sup>(1)</sup>	V <sub>CC</sub> = ±15 V		200		ns
t <sub>EN</sub>	Enable time <sup>(1)</sup>	V <sub>CC</sub> = ±15 V		300		ns
I <sub>IL(SHDN)</sub>	Shutdown pin low level leakage current	V <sub>CC</sub> = ±5 V to ±15 V, V <sub>SHDN</sub> = 0 V, REF = 0 V		18	25	μA
I <sub>IH(SHDN)</sub>	Shutdown pin high level leakage current	V <sub>CC</sub> = ±5 V to ±15 V, V <sub>SHDN</sub> = 3.3 V, REF = 0 V		110	130	μA

(1) Disable/enable time is defined as the time from when the shutdown signal is applied to the SHDN pin to when the supply current has reached half of its final value.

## TYPICAL CHARACTERISTICS

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I <sub>CC</sub>	vs Supply voltage	Figure 37
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## TYPICAL CHARACTERISTICS

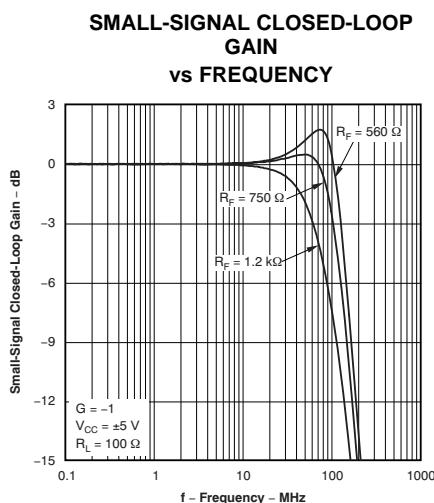


Figure 1.

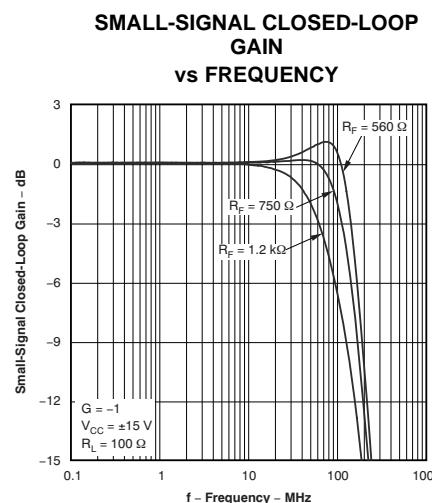


Figure 2.

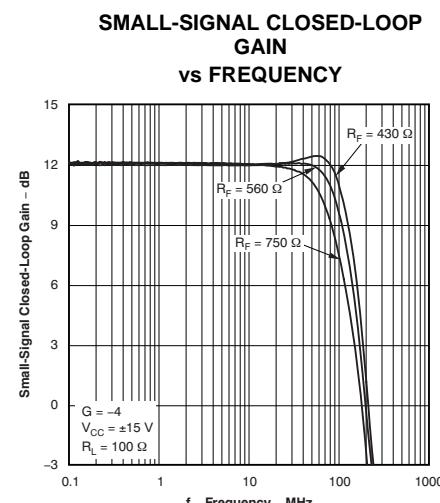


Figure 3.

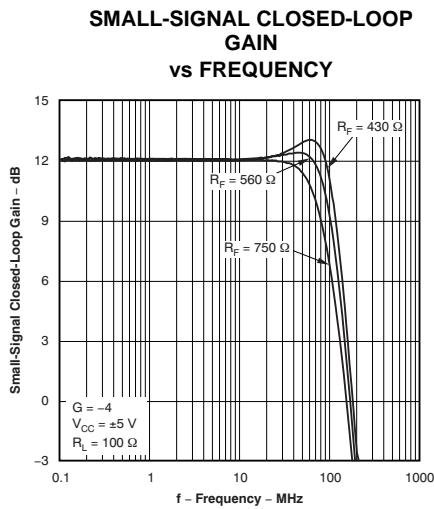


Figure 4.

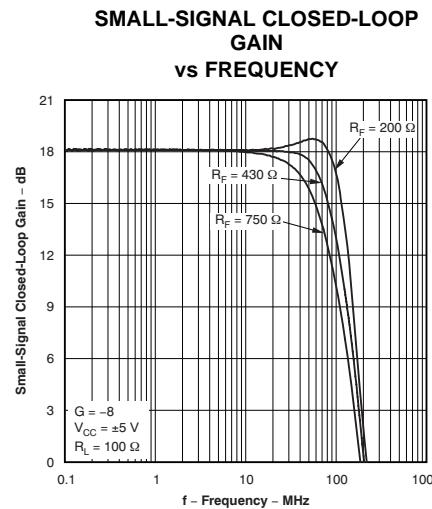


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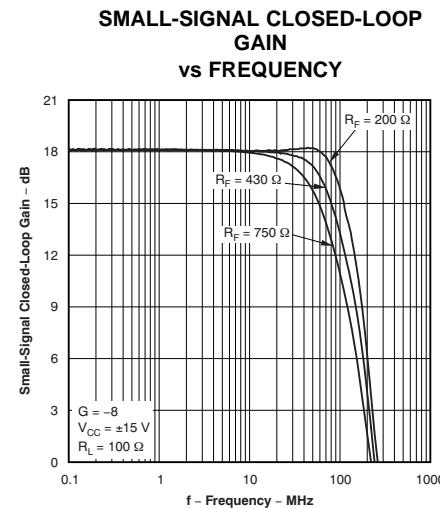


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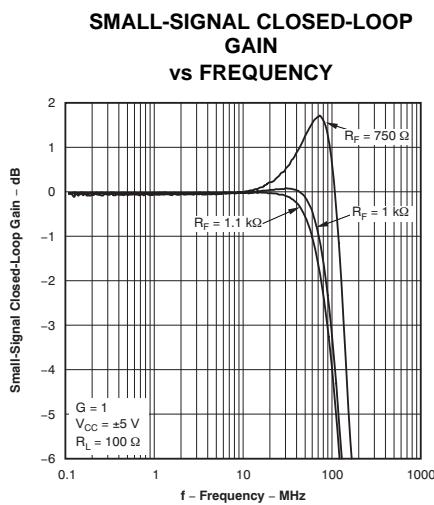


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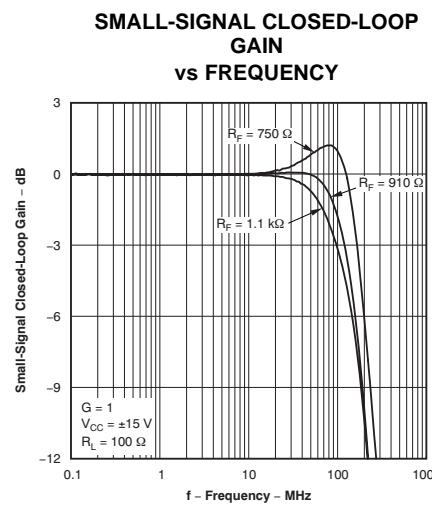


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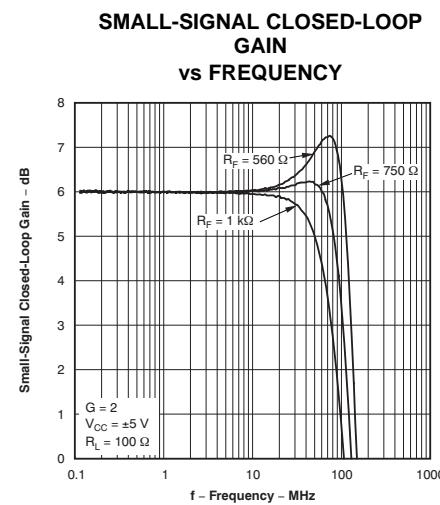
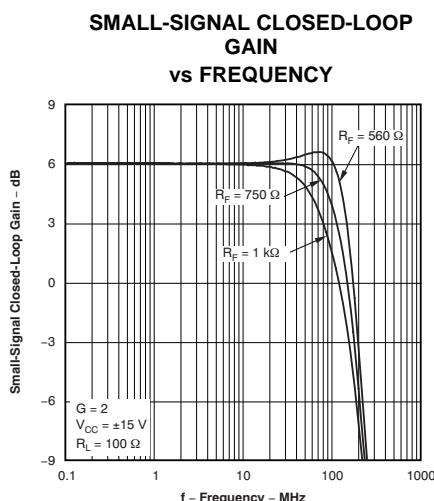
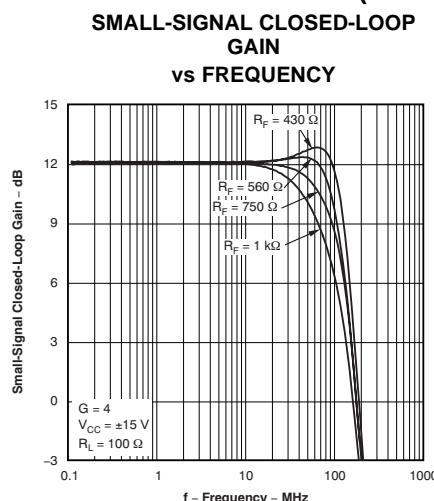
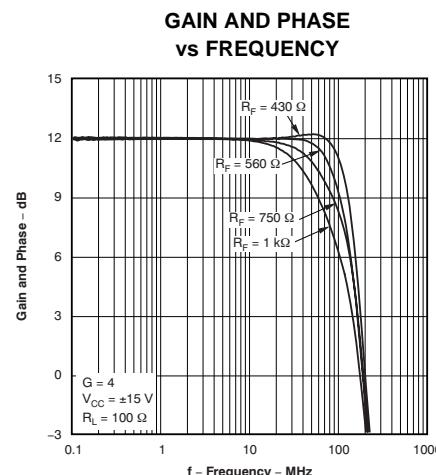
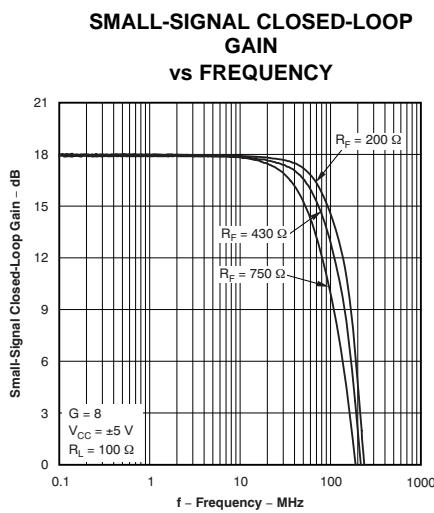
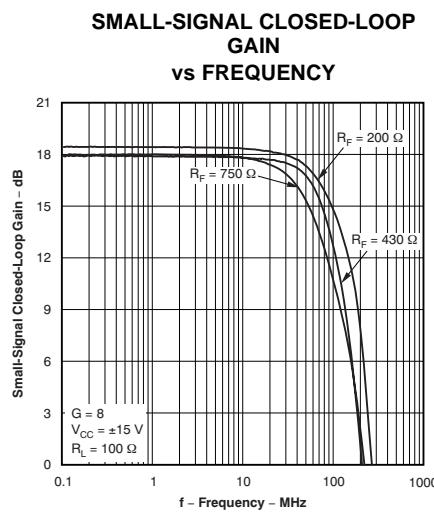
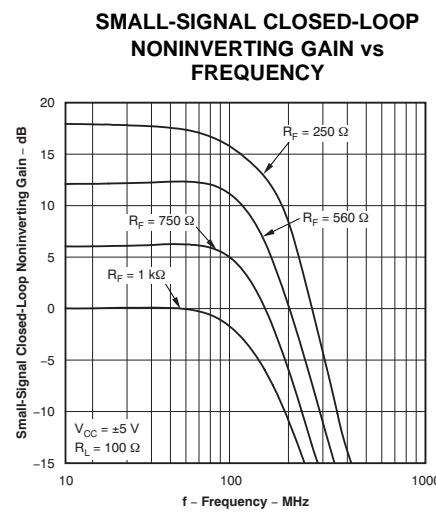
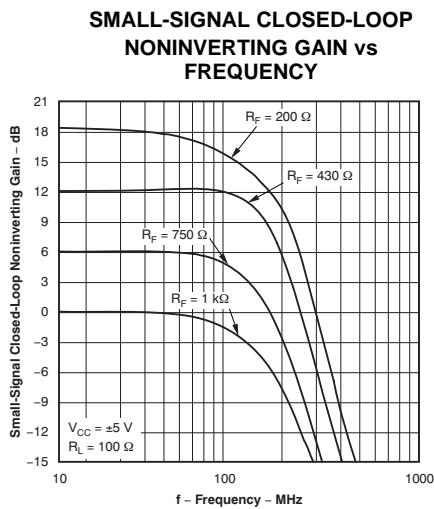
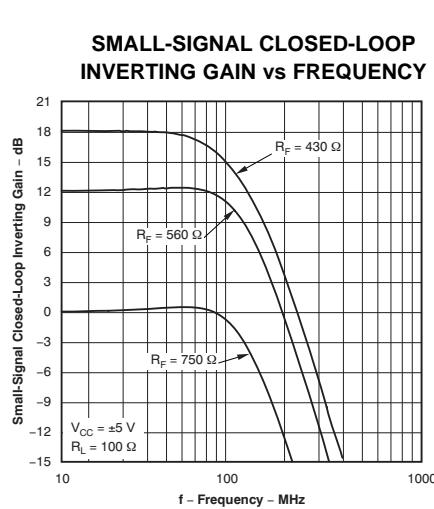
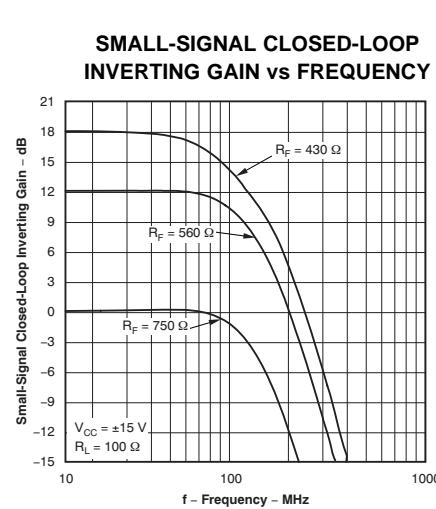


Figure 9.

**TYPICAL CHARACTERISTICS (continued)**

**Figure 10.**

**Figure 11.**

**Figure 12.**

**Figure 13.**

**Figure 14.**

**Figure 15.**

**Figure 16.**

**Figure 17.**

**Figure 18.**

## TYPICAL CHARACTERISTICS (continued)

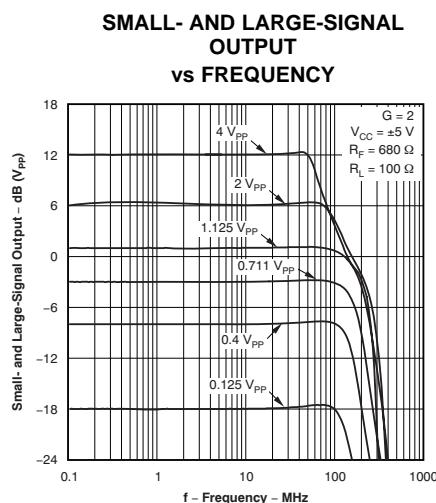


Figure 19.

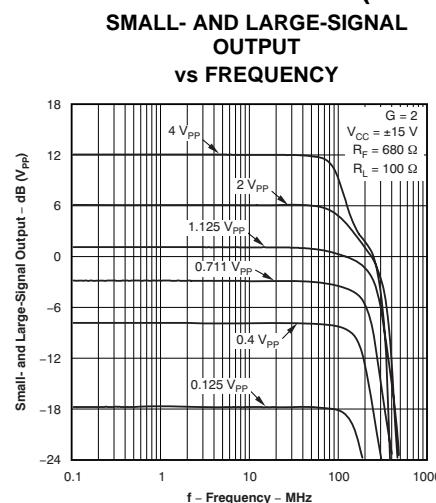


Figure 20.

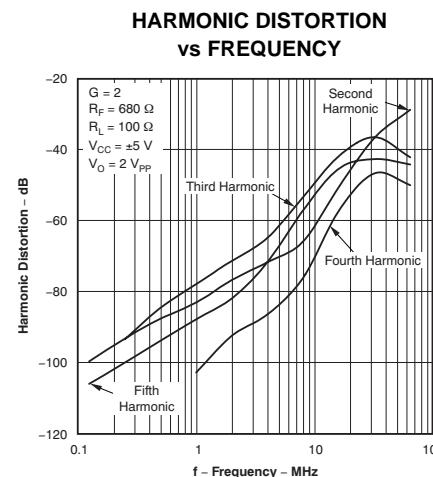


Figure 21.

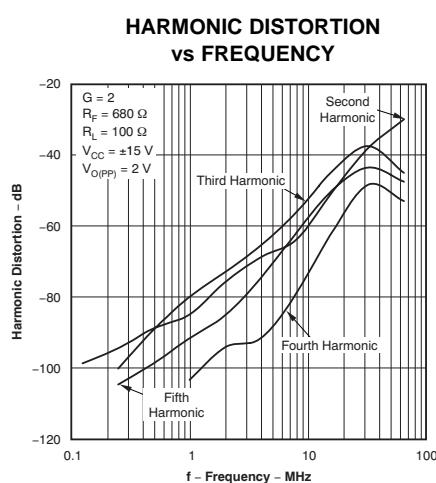


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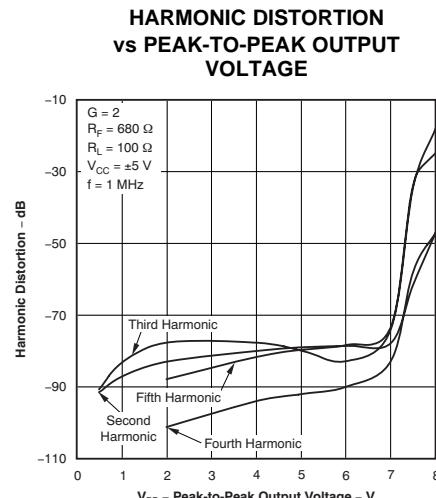


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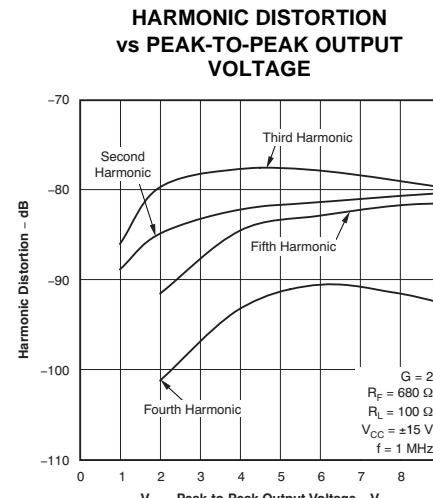


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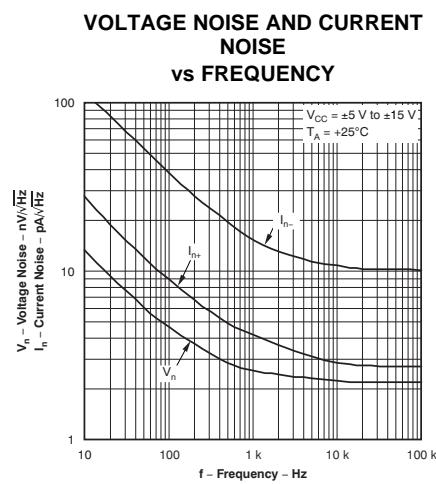


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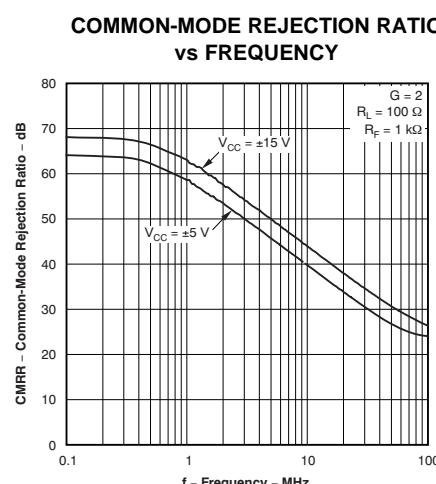


Figure 26.

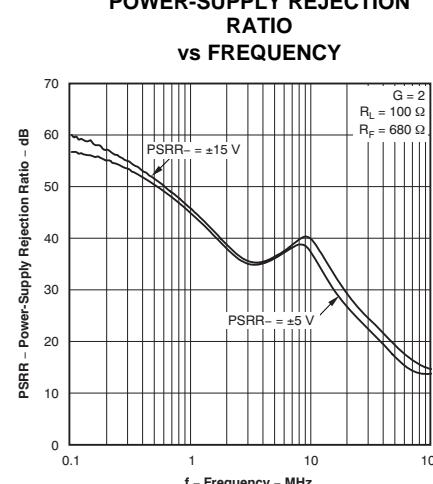
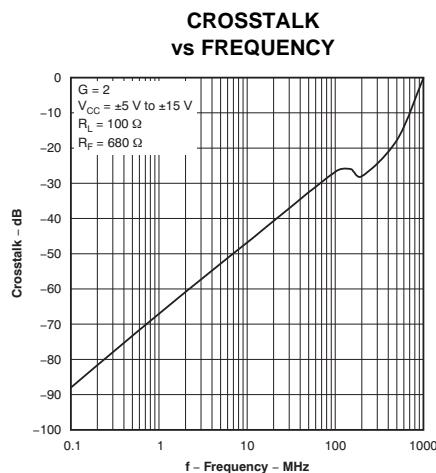
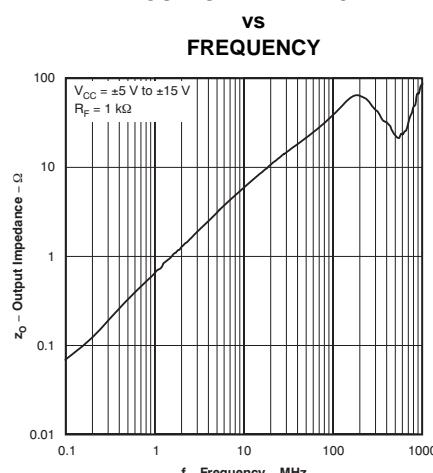
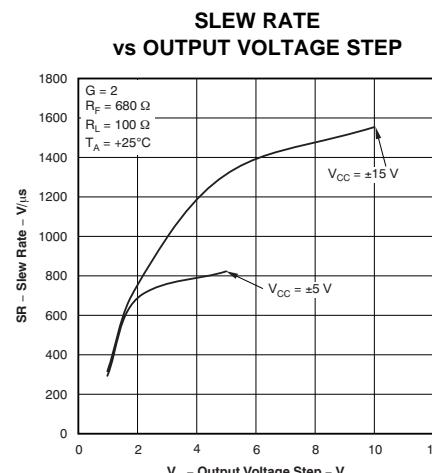
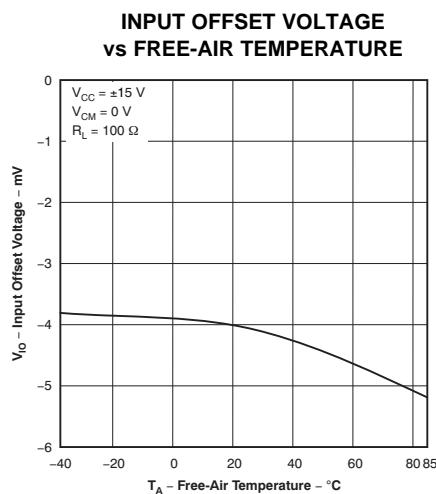
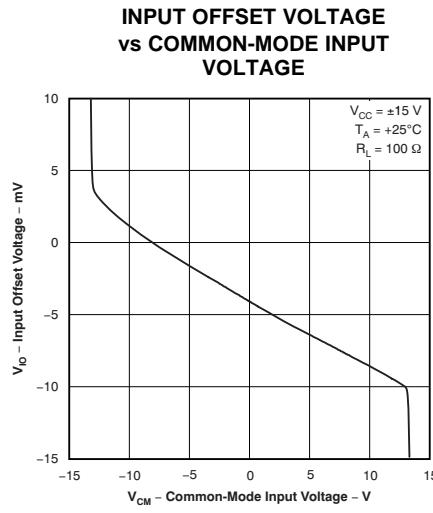
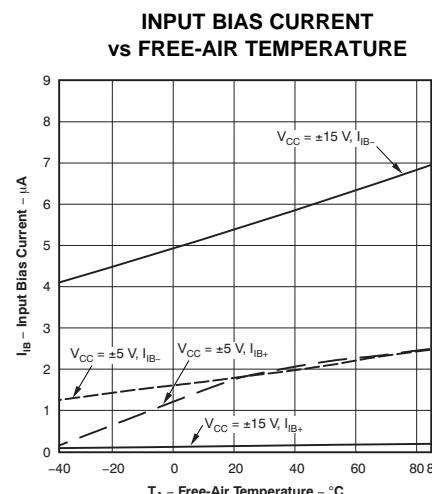
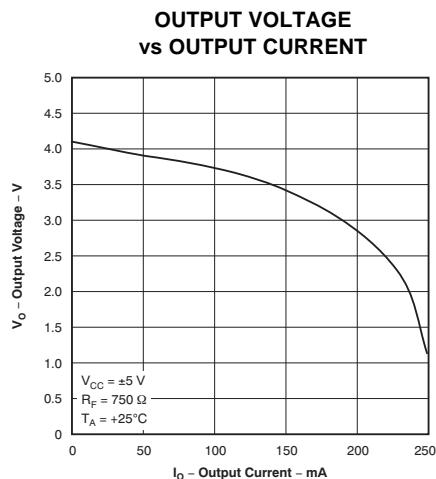
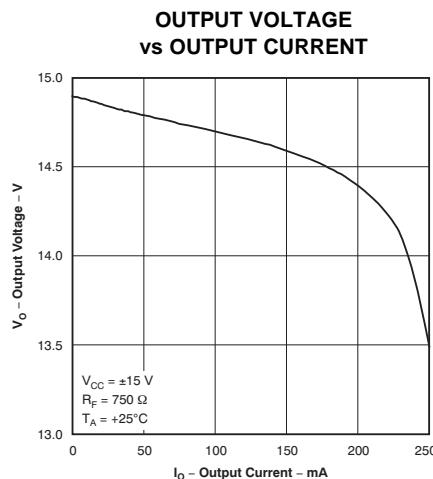
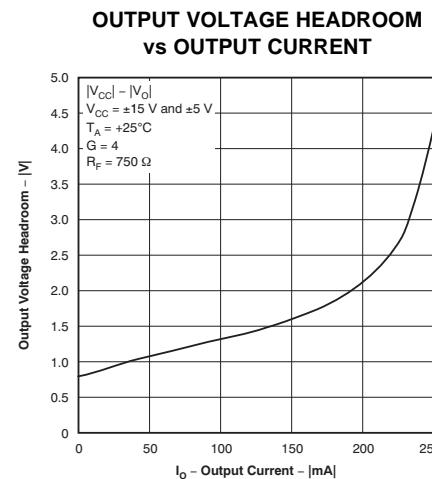


Figure 27.

**TYPICAL CHARACTERISTICS (continued)**
**OUTPUT IMPEDANCE**

**Figure 28.**

**Figure 29.**

**Figure 30.**

**Figure 31.**

**Figure 32.**

**Figure 33.**

**Figure 34.**

**Figure 35.**

**Figure 36.**

## TYPICAL CHARACTERISTICS (continued)

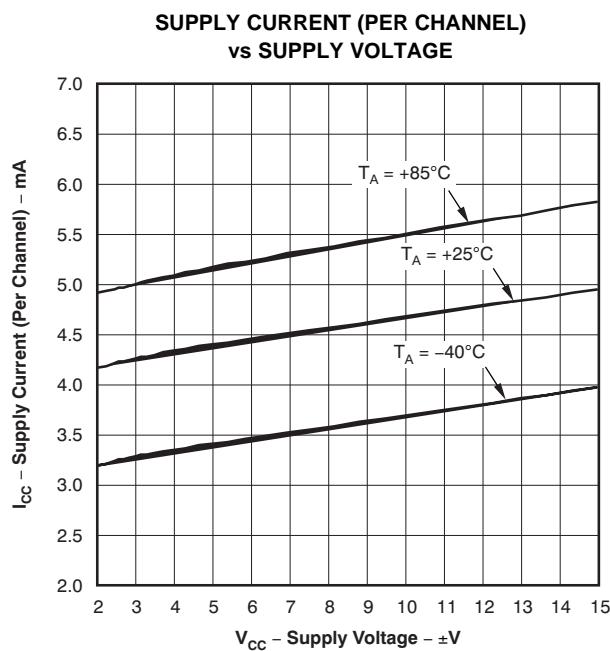


Figure 37.

## SHUTDOWN RESPONSE

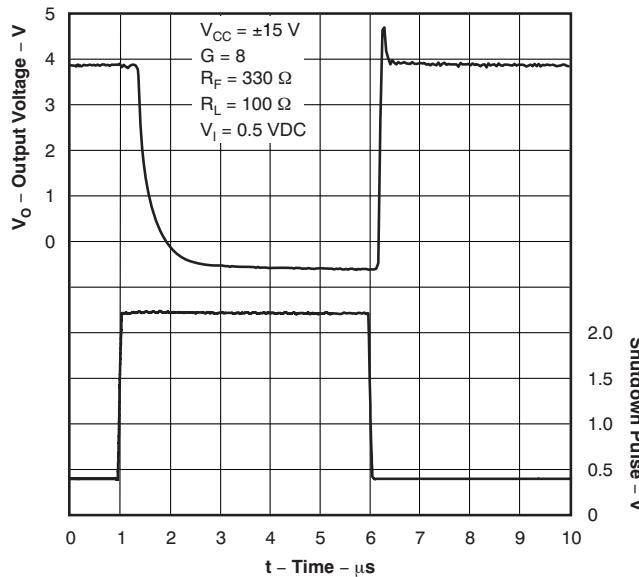


Figure 38.

## APPLICATION INFORMATION

### Maximum Slew Rate for Repetitive Signals

The THS3115 and THS3112 are recommended for high slew rate pulsed applications where the internal nodes of the amplifier have time to stabilize between pulses. It is recommended to have at least a 20-ns delay between pulses.

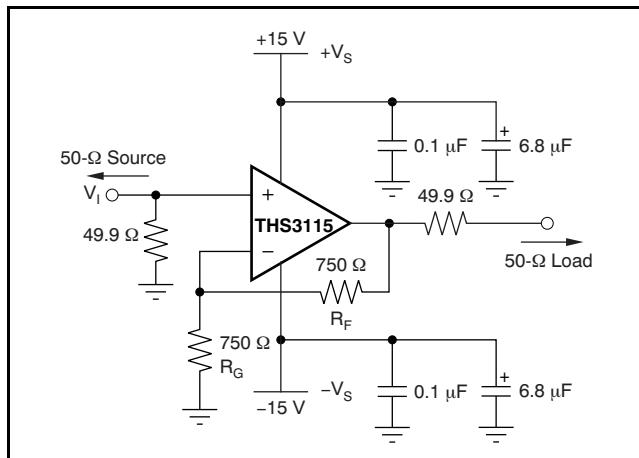
The THS3115 and THS3112 are not recommended for applications with repetitive signals (sine, square, sawtooth, or other) that exceed 900 V/μs. Using the part in these applications results in excessive current draw from the power supply and possible device damage.

For applications with high slew rate, repetitive signals, the [THS3091](#) and [THS3095](#) (single versions), or [THS3092](#) and [THS3096](#) (dual versions) are recommended.

### Wideband, Noninverting Operation

The THS3115 and THS3112 are unity gain stable 100-MHz current-feedback operational amplifiers, designed to operate from a  $\pm 5\text{-V}$  to  $\pm 15\text{-V}$  power supply.

[Figure 39](#) shows the THS3115 in a noninverting gain of 2-V/V configuration used to generate the typical characteristic curves. Most of the curves were characterized using signal sources with  $50\text{-}\Omega$  source impedance and with measurement equipment that presents a  $50\text{-}\Omega$  load impedance.



**Figure 39. Wideband, Noninverting Gain Configuration**

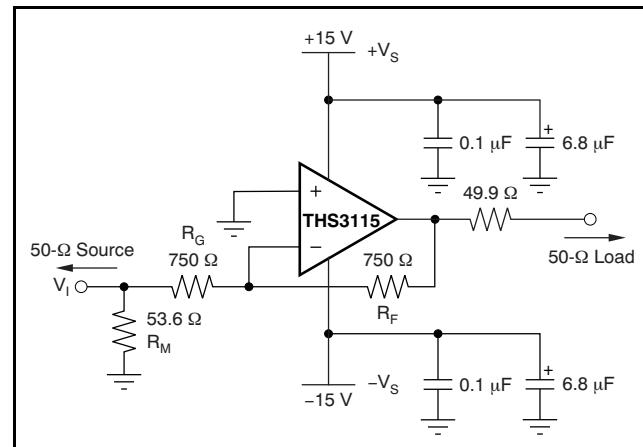
Current-feedback amplifiers are highly dependent on the feedback resistor  $R_F$  for maximum performance and stability. [Table 1](#) shows the optimal gain setting resistors  $R_F$  and  $R_G$  at different gains to give maximum bandwidth with minimal peaking in the frequency response. Higher bandwidths can be achieved, at the expense of added peaking in the frequency response, by using even lower values for  $R_F$ . Conversely, increasing  $R_F$  decreases the bandwidth, but stability is improved.

**Table 1. Recommended Resistor Values for Optimum Frequency Response**

THS3115 and THS3112 $R_F$ and $R_G$ VALUES FOR MINIMAL PEAKING WITH $R_L = 50\text{ }\Omega$ , $\pm 5\text{-V}$ to $\pm 15\text{-V}$ POWER SUPPLY		
GAIN (V/V)	$R_G$ ( $\Omega$ )	$R_F$ ( $\Omega$ )
1	—	1 k
2	750	750
4	187	560
8	28.7	200
-1	750	750
-4	140	560
-8	53.6	430

### Wideband, Inverting Operation

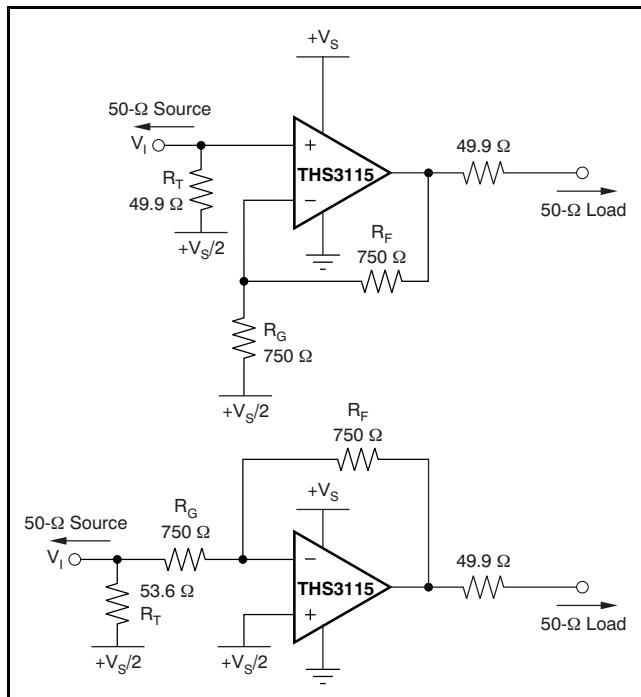
[Figure 40](#) shows the THS3115 in a typical inverting gain configuration designed for  $50\text{-}\Omega$  input/output.



**Figure 40. Wideband, Inverting Gain Configuration**

## Single-Supply Operation

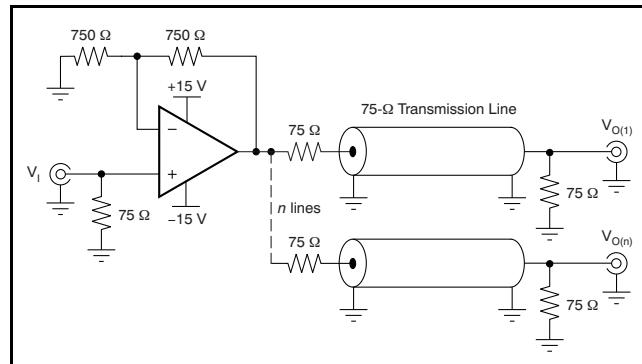
The THS3115 and THS3112 have the capability to operate from a single supply voltage ranging from 10 V to 30 V. When operating from a single power supply, biasing the input and output at mid-supply allows for the maximum output voltage swing. The circuits in [Figure 41](#) show inverting and noninverting amplifiers configured for single-supply operation.



**Figure 41. DC-Coupled, Single-Supply Operation**

## Video Distribution

The wide bandwidth, high slew rate, and high output drive current of the THS3115 and THS3112 match the demands for video distribution to deliver video signals down multiple cables. To ensure high signal quality with minimal degradation of performance, a 0.1-dB gain flatness should be at least 7x the passband frequency to minimize group delay variations from the amplifier. A high slew rate minimizes distortion of the video signal, and supports component video and RGB video signals that require fast transition times and fast settling times for high signal quality. [Figure 42](#) illustrates a typical video distribution amplifier application configuration.

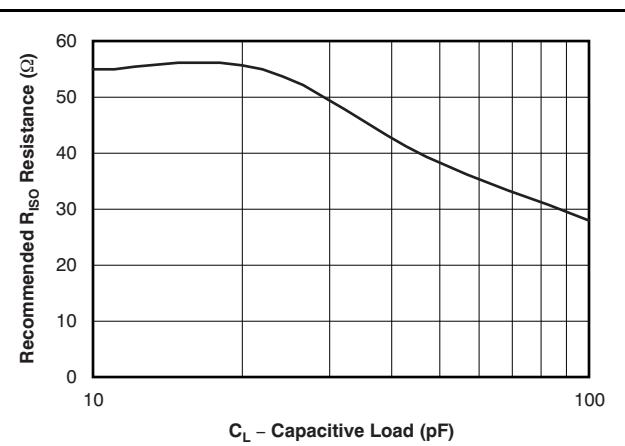


**Figure 42. Video Distribution Amplifier Application**

## Driving Capacitive Loads

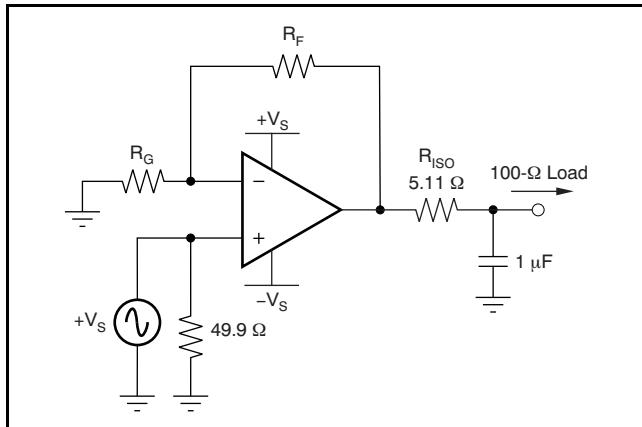
Applications such as FET drivers and line drivers can be highly capacitive and cause stability problems for high-speed amplifiers.

[Figure 43](#) through [Figure 49](#) show recommended methods for driving capacitive loads. The basic idea is to use a resistor or ferrite chip to isolate the phase shift at high frequency caused by the capacitive load from the amplifier feedback path. See [Figure 43](#) for recommended resistor values versus capacitive load.



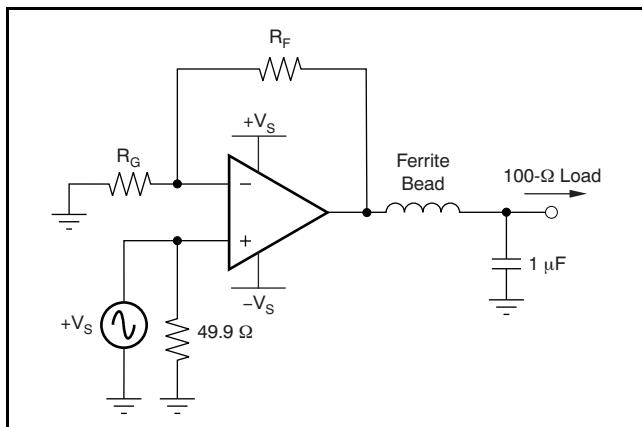
**Figure 43. Recommended  $R_{iso}$  vs Capacitive Load**

Placing a small series resistor,  $R_{ISO}$ , between the amplifier output and the capacitive load, as shown in [Figure 44](#), is an easy way of isolating the load capacitance.



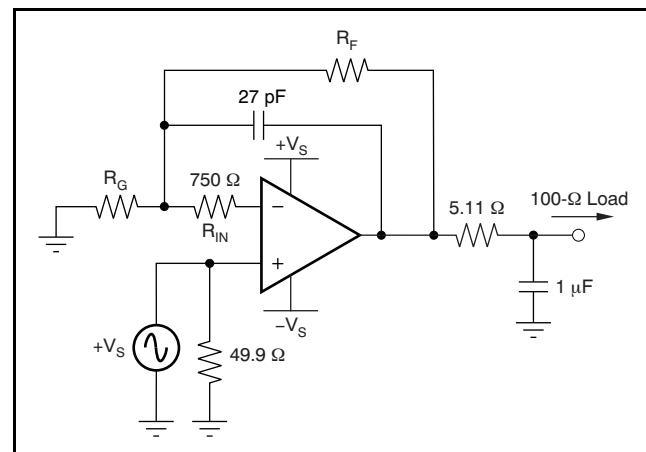
**Figure 44. Resistor to Isolate Capacitive Load**

Using a ferrite chip in place of  $R_{ISO}$ , as [Figure 45](#) shows, is another approach of isolating the output of the amplifier. The ferrite impedance characteristic versus frequency is useful to maintain the low frequency load independence of the amplifier while isolating the phase shift caused by the capacitance at high frequency. Use a ferrite with similar impedance to  $R_{ISO}$ , 20 Ω to 50 Ω, at 100 MHz and low impedance at dc.

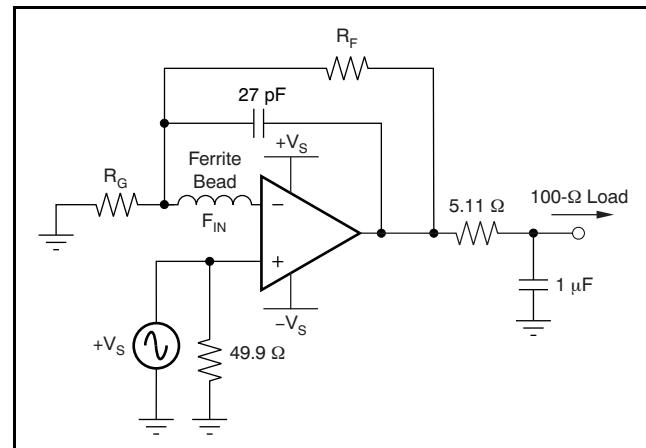


**Figure 45. Ferrite Bead to Isolate Capacitive Load**

[Figure 46](#) shows another method used to maintain the low-frequency load independence of the amplifier while isolating the phase shift caused by the capacitance at high frequency. At low frequency, feedback is mainly from the load side of  $R_{ISO}$ . At high frequency, the feedback is mainly via the 27-pF capacitor. The resistor  $R_{IN}$  in series with the negative input is used to stabilize the amplifier and should be equal to the recommended value of  $R_F$  at unity gain. Replacing  $R_{IN}$  with a ferrite of similar impedance at about 100 MHz as shown in [Figure 47](#) gives similar results with reduced dc offset and low frequency noise.



**Figure 46. Feedback Technique with Input Resistor for Capacitive Load**



**Figure 47. Feedback Technique with Input Ferrite Bead for Capacitive Load**

Figure 48 shows a configuration that uses two amplifiers in parallel to double the output drive current to larger capacitive loads. This technique is used when more output current is needed to charge and discharge the load faster as when driving large FET transistors.

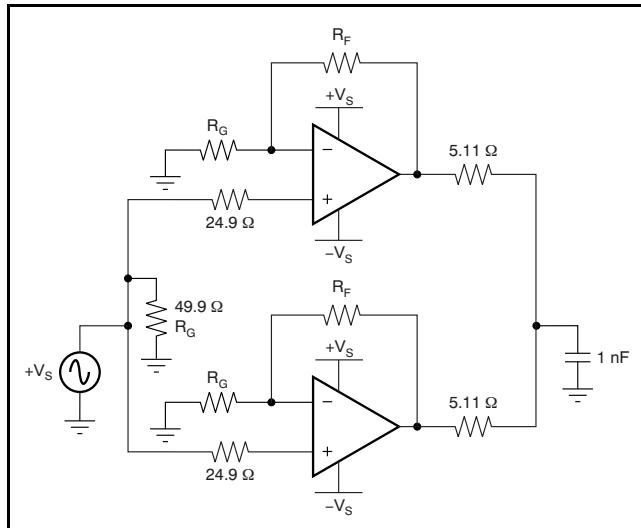


Figure 48. Parallel Amplifiers for Higher Output Drive

Figure 49 shows a push-pull FET driver circuit typical of ultrasound applications with isolation resistors to isolate the gate capacitance from the amplifier.

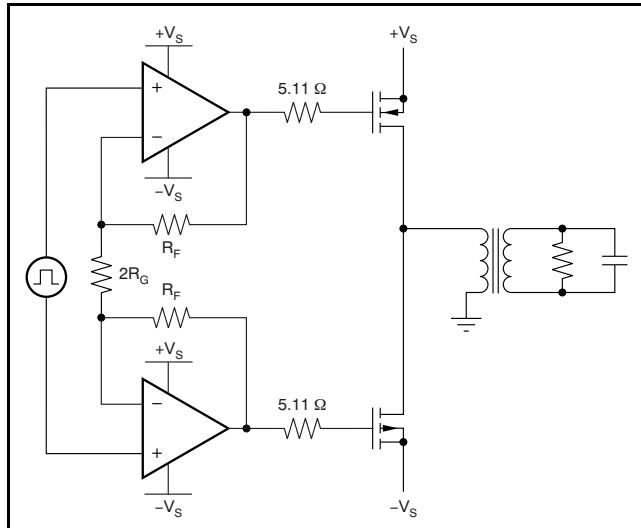


Figure 49. PowerFET Drive Circuit

### Saving Power with Shutdown Functionality and Setting Threshold Levels with the Reference Pin

The THS3115 features a shutdown pin (SHUTDOWN) that lowers the quiescent current from 4.9 mA/amp down to 300  $\mu$ A/amp, ideal for reducing system power.

The shutdown pin of the amplifier defaults to the REF pin voltage in the absence of an applied voltage, putting the amplifier in the normal on mode of operation. To turn off the amplifier in an effort to conserve power, the shutdown pin can be driven towards the positive rail. The threshold voltages for power-on and power-down (or shutdown) are relative to the supply rails and are given in the *Shutdown Characteristics* table. Below the *Enable* threshold voltage, the device is on. Above the *Disable* threshold voltage, the device is off. Behavior between these threshold voltages is not specified.

Note that this shutdown functionality is self-defining: the amplifier consumes less power in shutdown mode. The shutdown mode is not intended to provide a high-impedance output. In other words, the shutdown functionality is not intended to allow use as a 3-state bus driver. When in shutdown mode, the impedance looking back into the output of the amplifier is dominated by the feedback and gain setting resistors, but the output impedance of the device itself varies depending on the voltage applied to the outputs.

As with most current feedback amplifiers, the internal architecture places some limitations on the system when in shutdown mode. Most notably is the fact that the amplifier actually turns on if there is a  $\pm 0.7$  V or greater difference between the two input nodes (IN+ and IN-) of the amplifier. If this difference exceeds  $\pm 0.7$  V, the output of the amplifier creates an output voltage equal to approximately  $[(IN+ - IN-) - 0.7V] \times \text{Gain}$ . Also, if a voltage is applied to the output while in shutdown mode, the IN- node voltage is equal to  $V_{O(\text{applied})} \times R_G/(R_F + R_G)$ . For low gain configurations and a large applied voltage at the output, the amplifier may actually turn on because of the behavior described here.

The time delays associated with turning the device on and off are specified as the time it takes for the amplifier to reach either 10% or 90% of the final output voltage. The time delays are in the order of microseconds because the amplifier moves in and out of the linear mode of operation in these transitions.

## Power-Down Reference Pin Operation

In addition to the shutdown pin, the THS3115 features a reference pin (REF) which allows the user to control the enable or disable power-down voltage levels applied to the SHUTDOWN pin. In most split-supply applications, the reference pin is connected to ground. In either case, the user needs to be aware of voltage-level thresholds that apply to the shutdown pin. **Table 2** shows examples and illustrate the relationship between the reference voltage and the shutdown thresholds. In the table, the threshold levels are derived by the following equations:

$$\begin{aligned} \text{SHUTDOWN} &\leq \text{REF} + 0.8 \text{ V for enable} \\ \text{SHUTDOWN} &\geq \text{REF} + 2\text{V for disable} \end{aligned}$$

Where the usable range at the REF pin is:

$$V_{CC-} \leq V_{REF} \leq (V_{CC+} - 4\text{V})$$

The recommended mode of operation is to tie the REF pin to midrail, therefore setting the enable/disable thresholds to  $V_{(\text{midrail})} + 0.8 \text{ V}$  and  $V_{(\text{midrail})} = 2 \text{ V}$ , respectively.

**Table 2. Shutdown Threshold Voltage Levels**

SUPPLY VOLTAGE (V)	REFERENCE PIN VOLTAGE (V)	ENABLE LEVEL (V)	DISABLE LEVEL (V)
$\pm 15, \pm 5$	0	0.8	2.0
$\pm 15$	2.0	2.8	4.0
$\pm 15$	-2.0	-1.2	0
$\pm 5$	1.0	1.8	3.0
$\pm 5$	-1.0	-0.2	1.0
+30	15.0	15.8	17
+10	5.0	5.8	7.0

Note that if the REF pin is left unterminated, it floats to the positive rail and falls outside of the recommended operating range given above  $V_{CC-} \leq V_{REF} \leq (V_{CC+} - 4\text{V})$ . As a result, it no longer serves as a reliable reference for the SHUTDOWN pin, and the enable/disable thresholds given above no longer apply. If the SHUTDOWN pin is also left unterminated, it floats to the positive rail and the device is disabled. If balanced, split supplies are used ( $\pm V_{CC}$ ) and the REF and SHUTDOWN pins are grounded, the device is enabled.

## Printed-Circuit Board Layout Techniques for Optimal Performance

Achieving optimum performance with high-frequency amplifiers such as the THS3115 and THS3112 requires careful attention to board layout parasitic and external component types. Recommendations that optimize performance include:

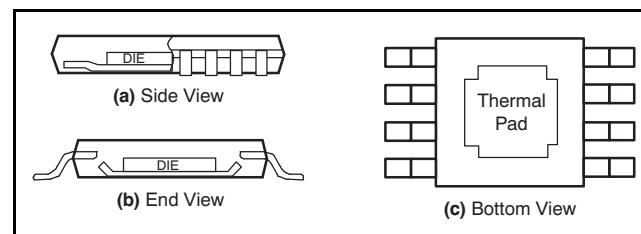
- Minimize parasitic capacitance to any ac ground for all of the signal I/O pins. Parasitic capacitance on the output and input pins can cause instability. To reduce unwanted capacitance, a window around the signal I/O pins should be opened in all of the ground and power planes around those pins. Otherwise, ground and power planes should be unbroken elsewhere on the board.
- Minimize the distance [0.25 inch, (6.4 mm)] from the power-supply pins to high-frequency 0.1- $\mu\text{F}$  and 100-pF decoupling capacitors. At the device pins, the ground and power plane layout should not be in close proximity to the signal I/O pins. Avoid narrow power and ground traces to minimize inductance between the pins and the decoupling capacitors. The power-supply connections should always be decoupled with these capacitors. Larger (6.8  $\mu\text{F}$  or more) tantalum decoupling capacitors, effective at lower frequencies, should also be used on the main supply pins. These capacitors may be placed somewhat farther from the device and may be shared among several devices in the same area of the printed circuit board (PCB).
- Careful selection and placement of external components preserve the high-frequency performance of the THS3115 and THS3112. Resistors should be a very low reactance type. Surface-mount resistors work best and allow a tighter overall layout. Again, keep the leads and PCB trace length as short as possible. Never use wirebound type resistors in a high-frequency application. Because the output pin and inverting input pins are the most sensitive to parasitic capacitance, always position the feedback and series output resistors, if any, as close as possible to the inverting input pins and output pins. Other network components, such as input termination resistors, should be placed close to the gain-setting resistors. Even with a low parasitic capacitance that shunts the external resistors, excessively high resistor values can create significant time constants that can degrade performance. Good axial metal-film or surface-mount resistors have approximately 0.2 pF in shunt with the resistor. For resistor values greater than 2.0 k $\Omega$ , this parasitic capacitance can add a pole and/or a zero that can affect circuit operation. Keep resistor values as low as possible, consistent with load driving considerations.

- Connections to other wideband devices on the board may be made with short direct traces or through onboard transmission lines. For short connections, consider the trace and the input to the next device as a lumped capacitive load. Relatively wide traces [0.05 inch (1.3 mm) to 0.1 inch (2.54 mm)] should be used, preferably with ground and power planes opened up around them. Estimate the total capacitive load and determine if isolation resistors on the outputs are necessary. Low parasitic capacitive loads (less than 4 pF) may not need an  $R_S$  because the THS3115 and THS3112 are nominally compensated to operate with a 2-pF parasitic load. Higher parasitic capacitive loads without an  $R_S$  are allowed as the signal gain increases (thus increasing the unloaded phase margin). If a long trace is required, and the 6-dB signal loss intrinsic to a doubly-terminated transmission line is acceptable, implement a matched-impedance transmission line using microstrip or stripline techniques (consult an ECL design handbook for microstrip and stripline layout techniques). A 50- $\Omega$  environment is not necessary onboard, and in fact, a higher impedance environment improves distortion as shown in the distortion versus load plots. With a characteristic board trace impedance based on board material and trace dimensions, a matching series resistor into the trace from the output of the THS3115/THS3112 is used as well as a terminating shunt resistor at the input of the destination device. Remember also that the terminating impedance is the parallel combination of the shunt resistor and the input impedance of the destination device: this total effective impedance should be set to match the trace impedance. If the 6-dB attenuation of a doubly-terminated transmission line is unacceptable, a long trace can be series-terminated at the source end only. Treat the trace as a capacitive load in this case. This configuration does not preserve signal integrity as well as a doubly-terminated line. If the input impedance of the destination device is low, there is some signal attenuation as a result of the voltage divider formed by the series output into the terminating impedance.

- Socketing a high-speed device such as the THS3115 and THS3112 is not recommended. The additional lead length and pin-to-pin capacitance introduced by the socket can create an extremely troublesome parasitic network which can make it almost impossible to achieve a smooth, stable frequency response. Best results are obtained by soldering the THS3115/THS3112 amplifiers directly onto the board.

### PowerPAD™ Design Considerations

The THS3115 and THS3112 are available in a thermally-enhanced PowerPAD family of packages. These packages are constructed using a downset leadframe upon which the die is mounted [see [Figure 50\(a\)](#) and [Figure 50\(b\)](#)]. This arrangement results in the lead frame being exposed as a thermal pad on the underside of the package [see [Figure 50\(c\)](#)]. Because this thermal pad has direct thermal contact with the die, excellent thermal performance can be achieved by providing a good thermal path away from the thermal pad. Note that devices such as the THS311x have no electrical connection between the PowerPAD and the die.

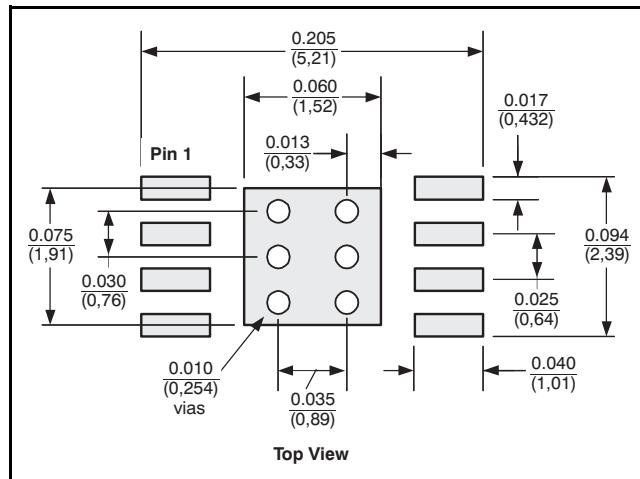


**Figure 50. Views of Thermally-Enhanced Package**

The PowerPAD package allows for both assembly and thermal management in one manufacturing operation. During the surface-mount solder operation (when the leads are being soldered), the thermal pad can also be soldered to a copper area underneath the package. Through the use of thermal paths within this copper area, heat can be conducted away from the package into either a ground plane or other heat dissipating device.

The PowerPAD package represents a breakthrough in combining the small area and ease of assembly of surface mount with the, heretofore, awkward mechanical methods of heatsinking.

## PowerPAD™ Layout Considerations



Dimensions are in inches (millimeters).

**Figure 51. DGN PowerPAD PCB Etch and Via Pattern**

Although there are many ways to properly heatsink the PowerPAD package, the following steps illustrate the recommended approach.

1. PCB with a top side etch pattern as shown in [Figure 51](#).
2. Place five holes in the area of the thermal pad. These holes should be 0.01 inch (0.254 mm) in diameter. Keep them small so that solder wicking through the holes is not a problem during reflow.
3. Additional vias may be placed anywhere along the thermal plane outside of the thermal pad area. These vias help dissipate the heat generated by the THS3115/THS3112 IC. These additional vias may be larger than the 0.01-inch (0.254-mm) diameter vias directly under the thermal pad. They can be larger because they are not in the thermal pad area to be soldered so that wicking is not a problem.
4. Connect all holes to the internal ground plane. Note that the PowerPAD is electrically isolated from the silicon and all leads. Connecting the PowerPAD to any potential voltage, such as  $V_{S-}$ , is acceptable as there is no electrical connection to the silicon.
5. When connecting these holes to the ground plane, do not use the typical web or spoke via connection methodology. Web connections have a high thermal resistance connection that is useful for slowing the heat transfer during soldering operations. This resistance makes the soldering of vias that have plane connections easier. In this application; however, low thermal resistance is desired for the most efficient heat

transfer. Therefore, the holes under the THS3115/THS3112 PowerPAD package should make the connection to the internal ground plane with a complete connection around the entire circumference of the plated-through hole.

6. The top-side solder mask should leave the terminals of the package and the thermal pad area with its five holes exposed. The bottom-side solder mask should cover the five holes of the thermal pad area. This configuration prevents solder from being pulled away from the thermal pad area during the reflow process.
7. Apply solder paste to the exposed thermal pad area and all of the IC terminals.
8. With these preparatory steps in place, the IC is simply placed in position and run through the solder reflow operation as any standard surface-mount component. This procedure results in a part that is properly installed.

## Power Dissipation and Thermal Considerations

The THS3115 and THS3112 incorporate automatic thermal shutoff protection. This protection circuitry shuts down the amplifier if the junction temperature exceeds approximately +160°C. When the junction temperature reduces to approximately +140°C, the amplifier turns on again. However, for maximum performance and reliability, the designer must take care to ensure that the design does not exceed a junction temperature of +125°C. Between +125°C and +150°C, damage does not occur, but the performance of the amplifier begins to degrade and long-term reliability suffers. The thermal characteristics of the device are dictated by the package and the PCB. Maximum power dissipation for a given package can be calculated using the following formula.

$$P_{DMax} = \frac{T_{max} - T_A}{\theta_{JA}}$$

where:

- $P_{DMax}$  is the maximum power dissipation in the amplifier (W)
- $T_{max}$  is the absolute maximum junction temperature (°C)
- $T_A$  is the ambient temperature (°C)

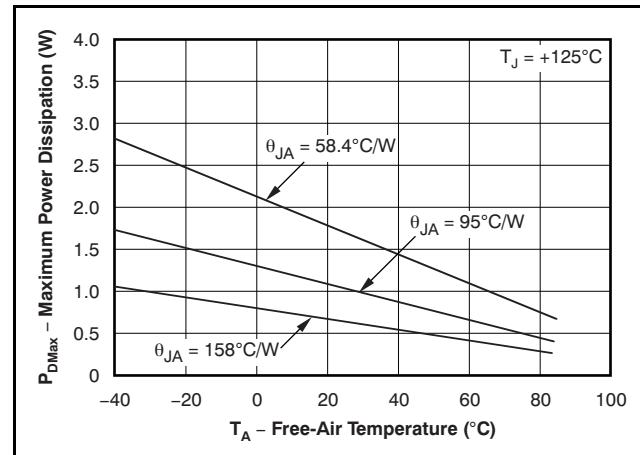
$$\theta_{JA} = \theta_{JC} + \theta_{CA}$$

where:

- $\theta_{JC}$  is the thermal coefficient from the silicon junctions to the case (°C/W)
- $\theta_{CA}$  is the thermal coefficient from the case to ambient air (°C/W)

For systems where heat dissipation is more critical, the THS3115 and THS3112 are also available in an 8-pin MSOP with PowerPAD package that offers even better thermal performance. The thermal coefficient for the PowerPAD packages are substantially improved over the traditional SOIC. Maximum power dissipation levels are depicted in Figure 52 for the available packages. The data for the PowerPAD packages assume a board layout that follows the PowerPAD layout guidelines discussed above and detailed in the PowerPAD application note (literature number [SLMA002](#)). Figure 52 also illustrates the effect of not soldering the PowerPAD to a PCB. The thermal impedance increases substantially, which may cause serious heat and performance issues. Always solder the PowerPAD to the PCB for optimum performance.

When determining whether or not the device satisfies the maximum power dissipation requirement, it is important to not only consider quiescent power dissipation, but also dynamic power dissipation. Often times, this type of dissipation is difficult to quantify because the signal pattern is inconsistent, but an estimate of the RMS power dissipation can provide visibility into a possible problem.



Results shown are with no air flow and PCB size of 3 in x 3 in (76.2 mm x 76.2 mm).

- $\theta_{JA} = 58.4^{\circ}\text{C/W}$  for 8-pin MSOP with PowerPAD (DGN package)
- $\theta_{JA} = 95^{\circ}\text{C/W}$  for 8-pin SOIC High-K test PCB (D package)
- $\theta_{JA} = 158^{\circ}\text{C/W}$  for 8-pin MSOP with PowerPAD without solder

**Figure 52. Maximum Power Dissipation vs. Ambient Temperature**

## REVISION HISTORY

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

### Changes from Revision B (October, 2009) to Revision C

	<b>Page</b>
• Corrected pin designations for TSSOP pinout drawing .....	1
• Deleted <i>Shutdown pin input levels</i> parameters from Recommended Operating Conditions table .....	3
• Added $V_{REF}$ parameter to Shutdown Characteristics table .....	5
• Added $V_{SHDN}$ parameter to Shutdown Characteristics table .....	5
• Changed reference to GND pin to "REF" in <i>Shutdown quiescent current</i> parameter test conditions in Shutdown Characteristics table .....	5
• Added REF = 0 V to test conditions for $I_{IL(SHDN)}$ parameter in Shutdown Characteristics table .....	5
• Added REF = 0 V to test conditions for $I_{IH(SHDN)}$ parameter in Shutdown Characteristics table .....	5
• Revised <i>Saving Power with Shutdown Functionality and Setting Threshold Levels with the Reference Pin</i> section .....	14
• Updated <i>Power-Down Reference Pin Operation</i> section; changed references to $V_{S-}$ , $V_{S+}$ to $V_{CC-}$ , $V_{CC+}$ .....	15

### Changes from Revision A (January, 2009) to Revision B

	<b>Page</b>
• Updated document format to conform to current standards .....	1
• Deleted lead temperature specification from <i>Absolute Maximum Ratings</i> table .....	2
• Added <i>Application Information</i> section .....	11

**PACKAGING INFORMATION**

Orderable part number	Status (1)	Material type (2)	Package   Pins	Package qty   Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
<a href="#">THS3112CD</a>	Active	Production	SOIC (D)   8	75   TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	3112C
THS3112CD.A	Active	Production	SOIC (D)   8	75   TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	3112C
<a href="#">THS3112CDDA</a>	Active	Production	SO PowerPAD (DDA)   8	75   TUBE	Yes	SN	Level-1-260C-UNLIM	0 to 70	3112C
THS3112CDDA.A	Active	Production	SO PowerPAD (DDA)   8	75   TUBE	Yes	SN	Level-1-260C-UNLIM	0 to 70	3112C
<a href="#">THS3112CDR</a>	Active	Production	SOIC (D)   8	2500   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	3112C
THS3112CDR.A	Active	Production	SOIC (D)   8	2500   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	3112C
<a href="#">THS3112ID</a>	Active	Production	SOIC (D)   8	75   TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	3112I
THS3112ID.A	Active	Production	SOIC (D)   8	75   TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	3112I
<a href="#">THS3112IDDA</a>	Active	Production	SO PowerPAD (DDA)   8	75   TUBE	Yes	SN	Level-1-260C-UNLIM	-40 to 85	3112I
THS3112IDDA.A	Active	Production	SO PowerPAD (DDA)   8	75   TUBE	Yes	SN	Level-1-260C-UNLIM	-40 to 85	3112I
<a href="#">THS3112IDDAR</a>	Active	Production	SO PowerPAD (DDA)   8	2500   LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 85	3112I
THS3112IDDAR.A	Active	Production	SO PowerPAD (DDA)   8	2500   LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 85	3112I
<a href="#">THS3115CPWP</a>	Active	Production	HTSSOP (PWP)   14	90   TUBE	Yes	NIPDAU	Level-2-260C-1 YEAR	0 to 70	HS3115C
THS3115CPWP.A	Active	Production	HTSSOP (PWP)   14	90   TUBE	Yes	NIPDAU	Level-2-260C-1 YEAR	0 to 70	HS3115C
<a href="#">THS3115CPWPR</a>	Active	Production	HTSSOP (PWP)   14	2000   LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	0 to 70	HS3115C
THS3115CPWPR.A	Active	Production	HTSSOP (PWP)   14	2000   LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	0 to 70	HS3115C
<a href="#">THS3115ID</a>	Active	Production	SOIC (D)   14	50   TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	THS3115I
THS3115ID.A	Active	Production	SOIC (D)   14	50   TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	THS3115I
<a href="#">THS3115IPWP</a>	Active	Production	HTSSOP (PWP)   14	90   TUBE	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	HS3115I
THS3115IPWP.A	Active	Production	HTSSOP (PWP)   14	90   TUBE	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	HS3115I
<a href="#">THS3115IPWPR</a>	Active	Production	HTSSOP (PWP)   14	2000   LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	HS3115I
THS3115IPWPR.A	Active	Production	HTSSOP (PWP)   14	2000   LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	HS3115I

<sup>(1)</sup> **Status:** For more details on status, see our [product life cycle](#).

**(2) Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

**(3) RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

**(4) Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

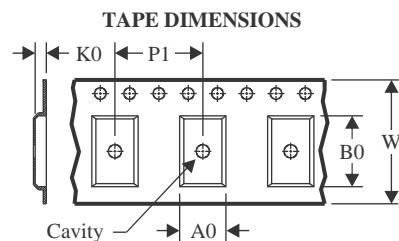
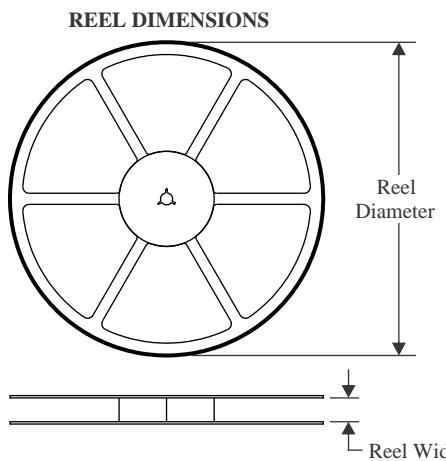
**(5) MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

**(6) Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

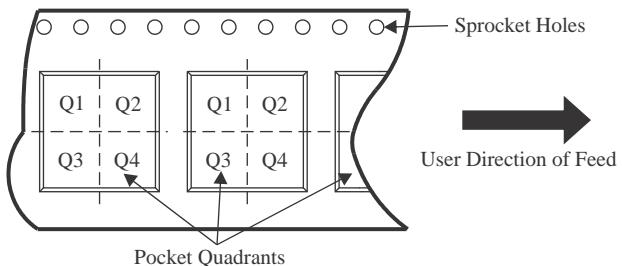
Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

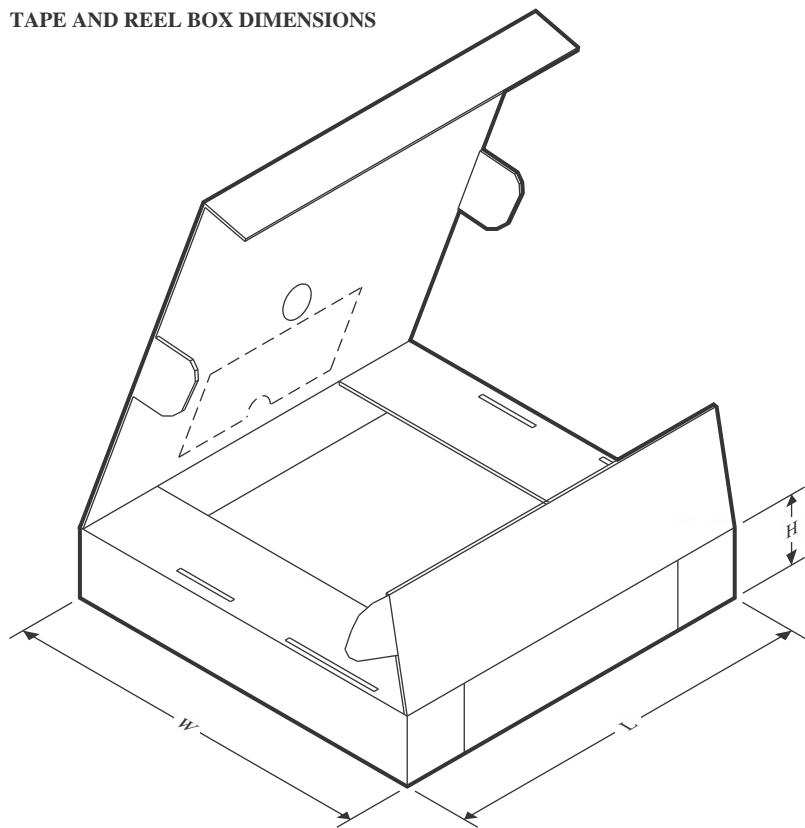
**TAPE AND REEL INFORMATION**


A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

**QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE**


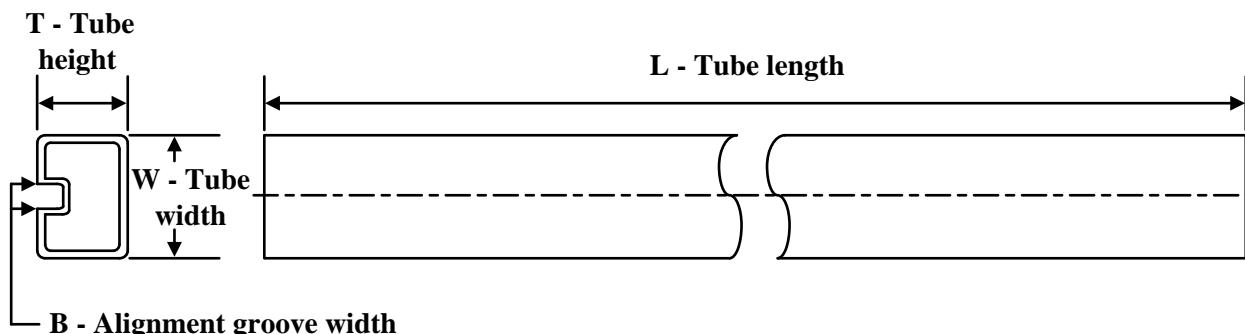
\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
THS3112CDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
THS3112IDDAR	SO PowerPAD	DDA	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
THS3115CPWPR	HTSSOP	PWP	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
THS3115IPWPR	HTSSOP	PWP	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1

**TAPE AND REEL BOX DIMENSIONS**


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
THS3112CDR	SOIC	D	8	2500	350.0	350.0	43.0
THS3112IDDAR	SO PowerPAD	DDA	8	2500	350.0	350.0	43.0
THS3115CPWPR	HTSSOP	PWP	14	2000	350.0	350.0	43.0
THS3115IPWPR	HTSSOP	PWP	14	2000	350.0	350.0	43.0

**TUBE**


\*All dimensions are nominal

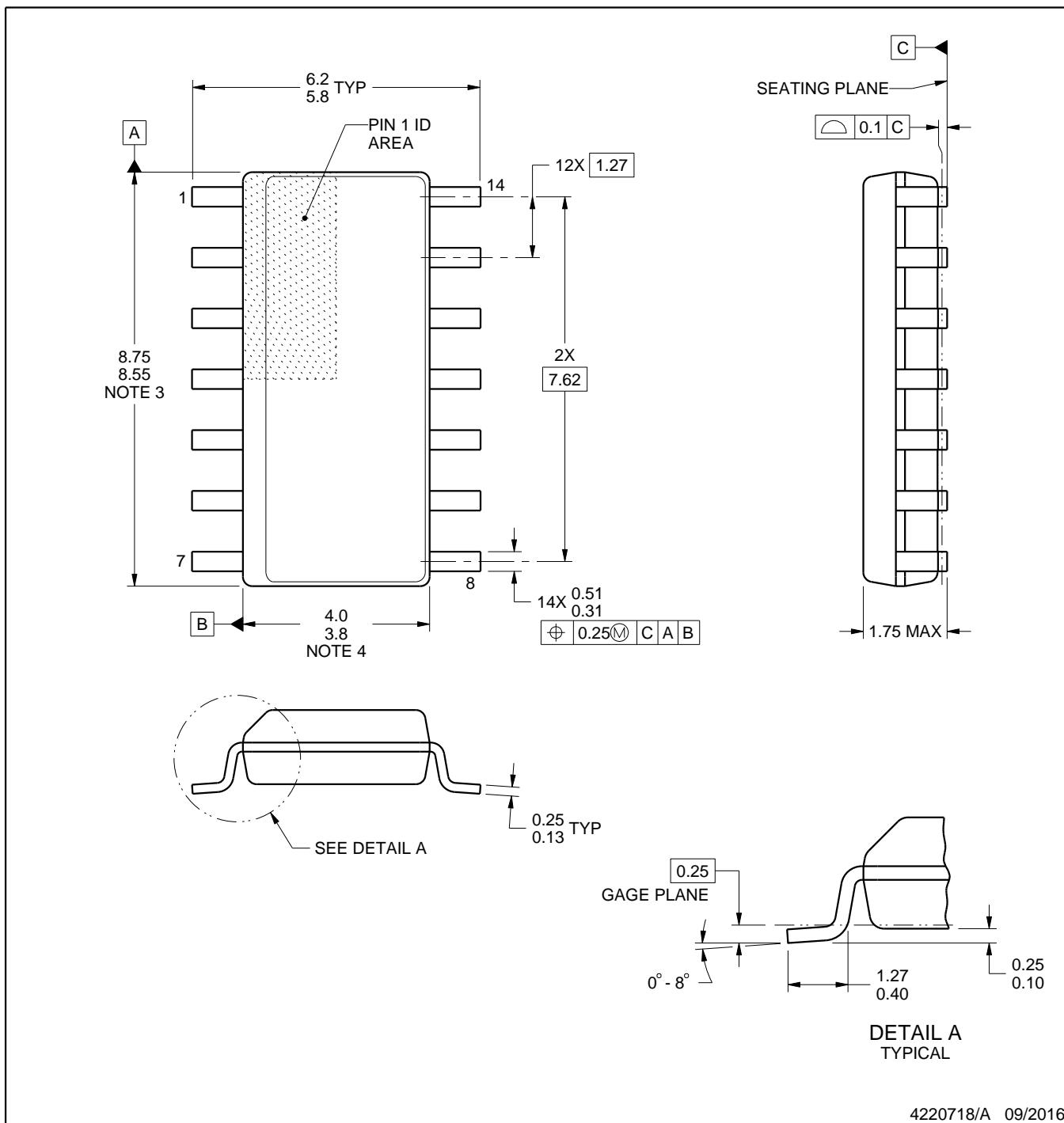
Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T ( $\mu$ m)	B (mm)
THS3112CD	D	SOIC	8	75	505.46	6.76	3810	4
THS3112CD.A	D	SOIC	8	75	505.46	6.76	3810	4
THS3112CDDA	DDA	HSOIC	8	75	505.46	6.76	3810	4
THS3112CDDA.A	DDA	HSOIC	8	75	505.46	6.76	3810	4
THS3112ID	D	SOIC	8	75	505.46	6.76	3810	4
THS3112ID.A	D	SOIC	8	75	505.46	6.76	3810	4
THS3112IDDA	DDA	HSOIC	8	75	505.46	6.76	3810	4
THS3112IDDA.A	DDA	HSOIC	8	75	505.46	6.76	3810	4
THS3115CPWP	PWP	HTSSOP	14	90	530	10.2	3600	3.5
THS3115CPWP.A	PWP	HTSSOP	14	90	530	10.2	3600	3.5
THS3115ID	D	SOIC	14	50	505.46	6.76	3810	4
THS3115ID.A	D	SOIC	14	50	505.46	6.76	3810	4
THS3115IPWP	PWP	HTSSOP	14	90	530	10.2	3600	3.5
THS3115IPWP.A	PWP	HTSSOP	14	90	530	10.2	3600	3.5

# PACKAGE OUTLINE

D0014A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



## NOTES:

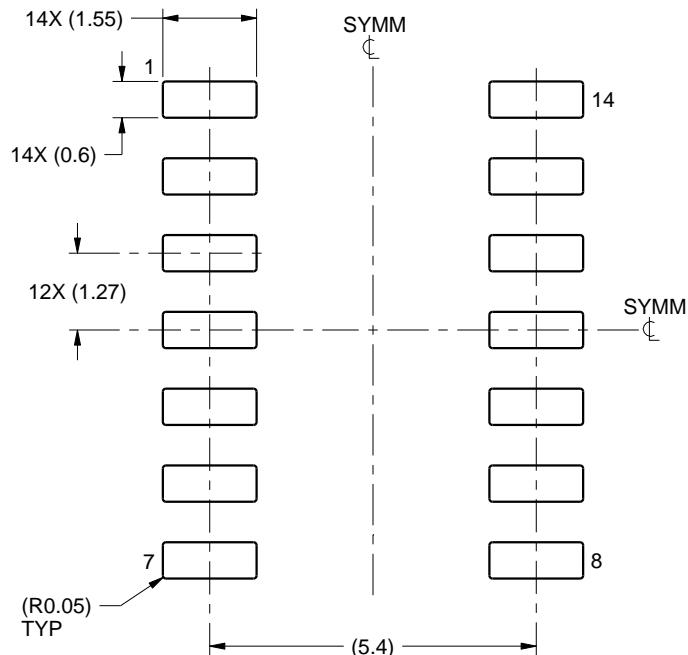
1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm, per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm, per side.
5. Reference JEDEC registration MS-012, variation AB.

# EXAMPLE BOARD LAYOUT

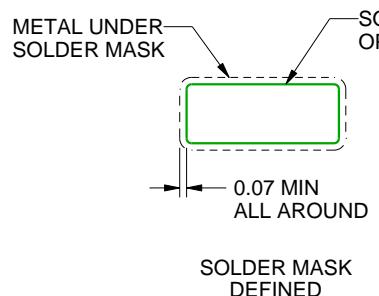
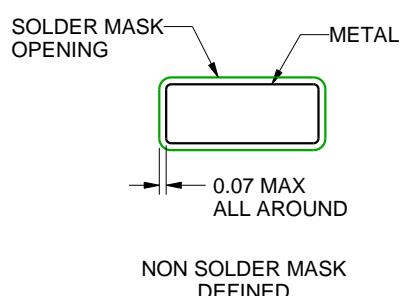
D0014A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



LAND PATTERN EXAMPLE  
SCALE:8X



SOLDER MASK DETAILS

4220718/A 09/2016

NOTES: (continued)

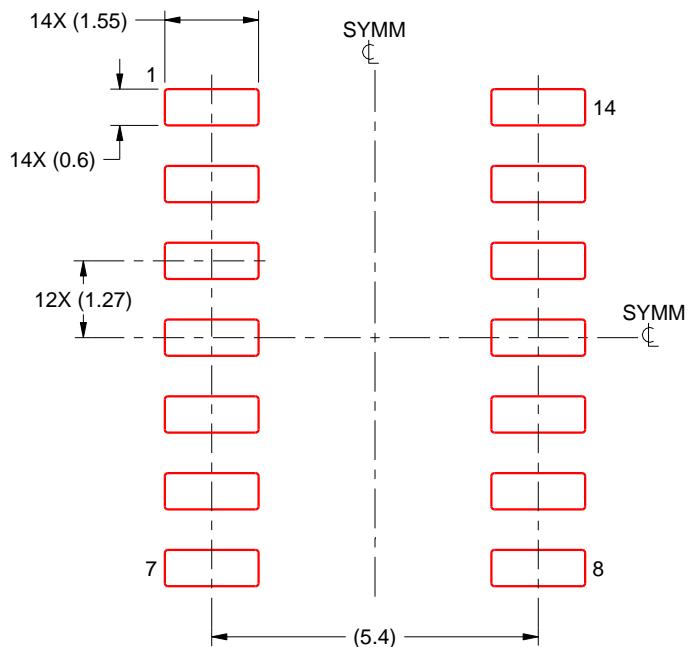
6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

## EXAMPLE STENCIL DESIGN

**D0014A**

## **SOIC - 1.75 mm max height**

## SMALL OUTLINE INTEGRATED CIRCUIT



**SOLDER PASTE EXAMPLE  
BASED ON 0.125 mm THICK STENCIL  
SCALE:8X**

4220718/A 09/2016

#### NOTES: (continued)

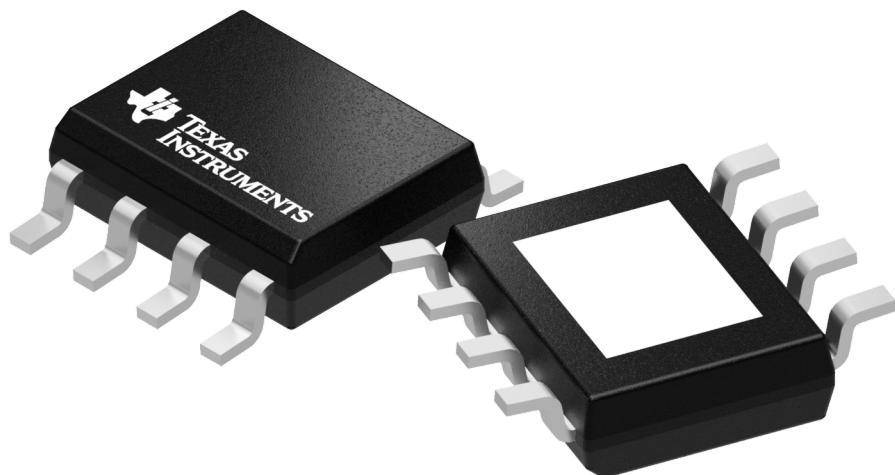
8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

## GENERIC PACKAGE VIEW

DDA 8

PowerPAD™ SOIC - 1.7 mm max height

PLASTIC SMALL OUTLINE



Images above are just a representation of the package family, actual package may vary.  
Refer to the product data sheet for package details.

4202561/G

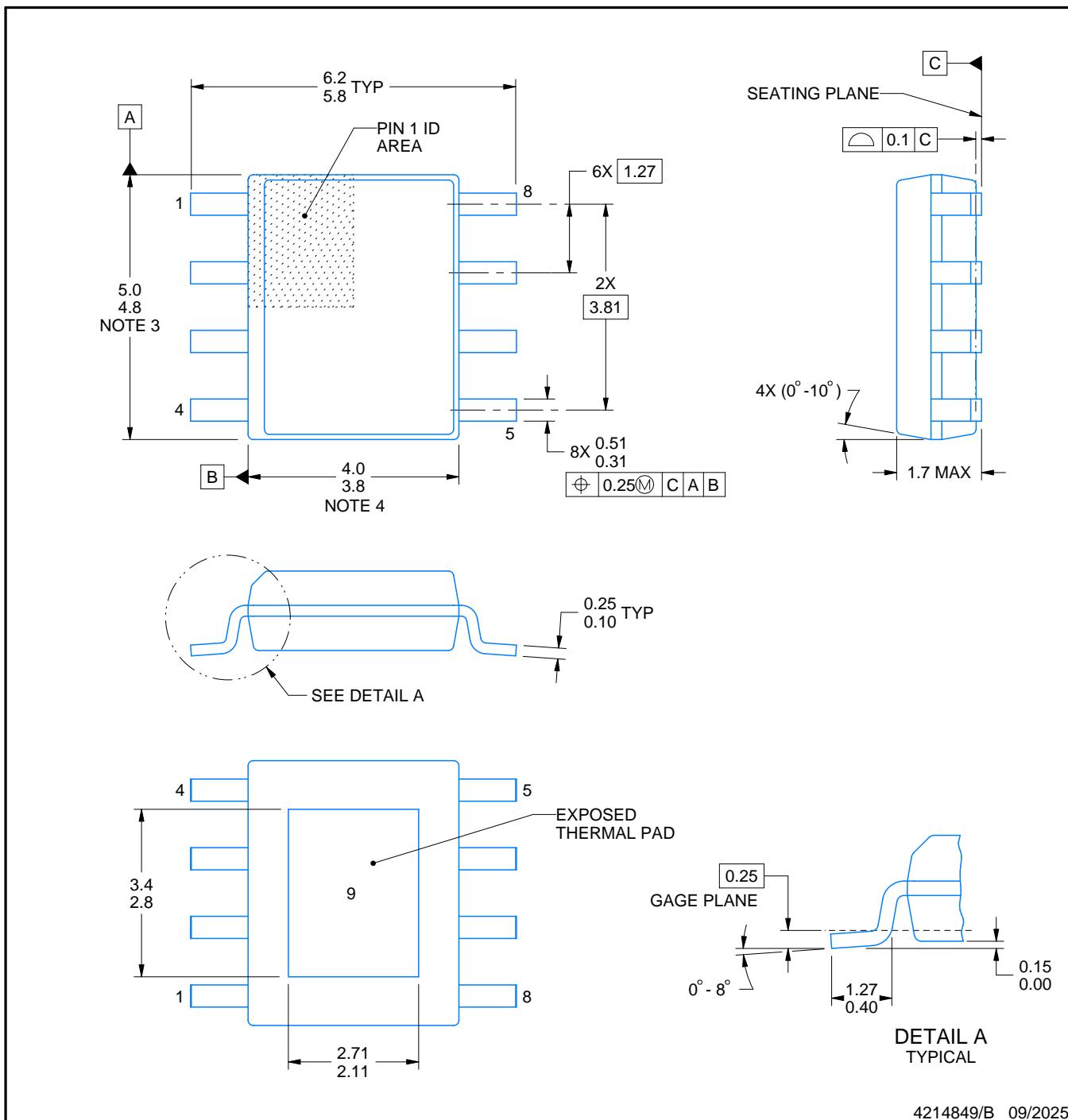
DDA0008B



# PACKAGE OUTLINE

PowerPAD™ SOIC - 1.7 mm max height

PLASTIC SMALL OUTLINE



4214849/B 09/2025

PowerPAD is a trademark of Texas Instruments.

NOTES:

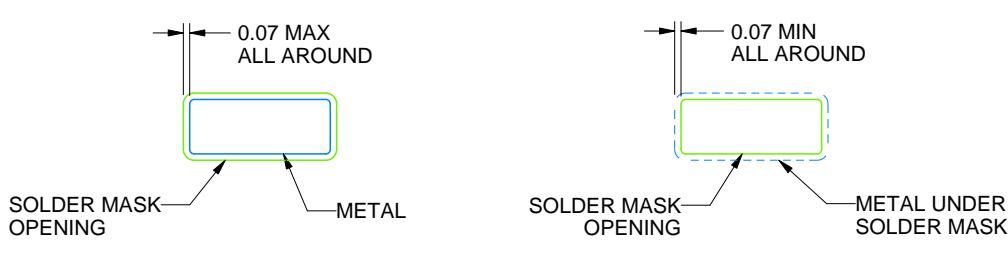
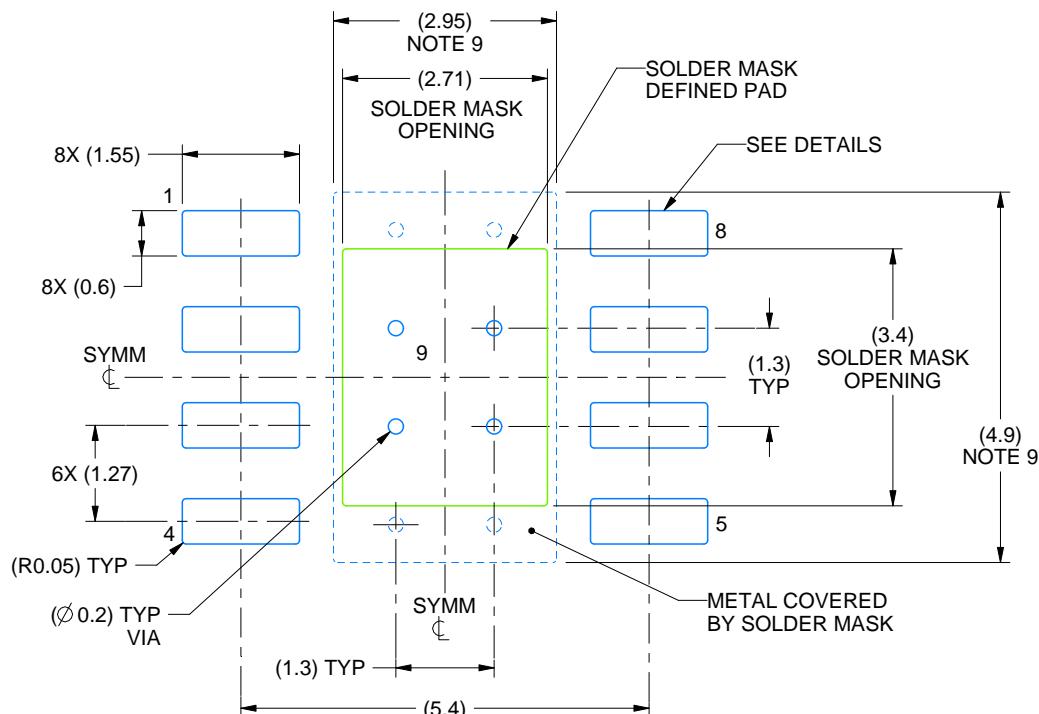
- All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- This drawing is subject to change without notice.
- This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
- This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- Reference JEDEC registration MS-012.

# EXAMPLE BOARD LAYOUT

DDA0008B

PowerPAD™ SOIC - 1.7 mm max height

PLASTIC SMALL OUTLINE



SOLDER MASK DETAILS  
PADS 1-8

4214849/B 09/2025

NOTES: (continued)

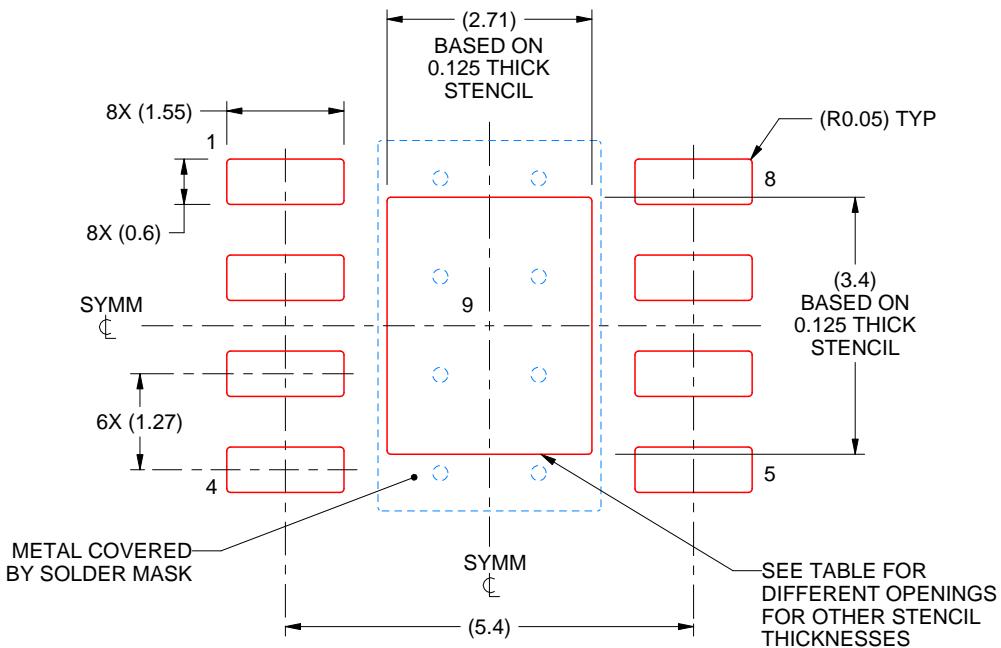
6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.
8. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature numbers SLMA002 ([www.ti.com/lit/slma002](http://www.ti.com/lit/slma002)) and SLMA004 ([www.ti.com/lit/slma004](http://www.ti.com/lit/slma004)).
9. Size of metal pad may vary due to creepage requirement.
10. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.

# EXAMPLE STENCIL DESIGN

DDA0008B

PowerPAD™ SOIC - 1.7 mm max height

PLASTIC SMALL OUTLINE



SOLDER PASTE EXAMPLE  
EXPOSED PAD  
100% PRINTED SOLDER COVERAGE BY AREA  
SCALE:10X

STENCIL THICKNESS	SOLDER STENCIL OPENING
0.1	3.03 X 3.80
0.125	2.71 X 3.40 (SHOWN)
0.150	2.47 X 3.10
0.175	2.29 X 2.87

4214849/B 09/2025

NOTES: (continued)

11. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
12. Board assembly site may have different recommendations for stencil design.

## GENERIC PACKAGE VIEW

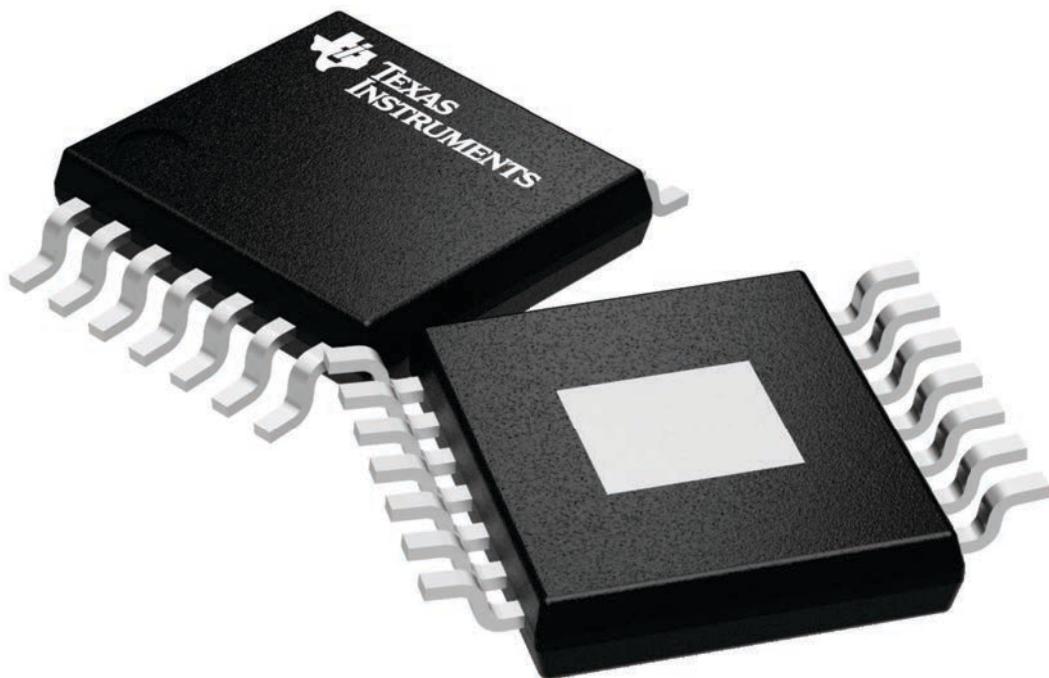
### PWP 14

### PowerPAD TSSOP - 1.2 mm max height

4.4 x 5.0, 0.65 mm pitch

PLASTIC SMALL OUTLINE

This image is a representation of the package family, actual package may vary.  
Refer to the product data sheet for package details.



4224995/A

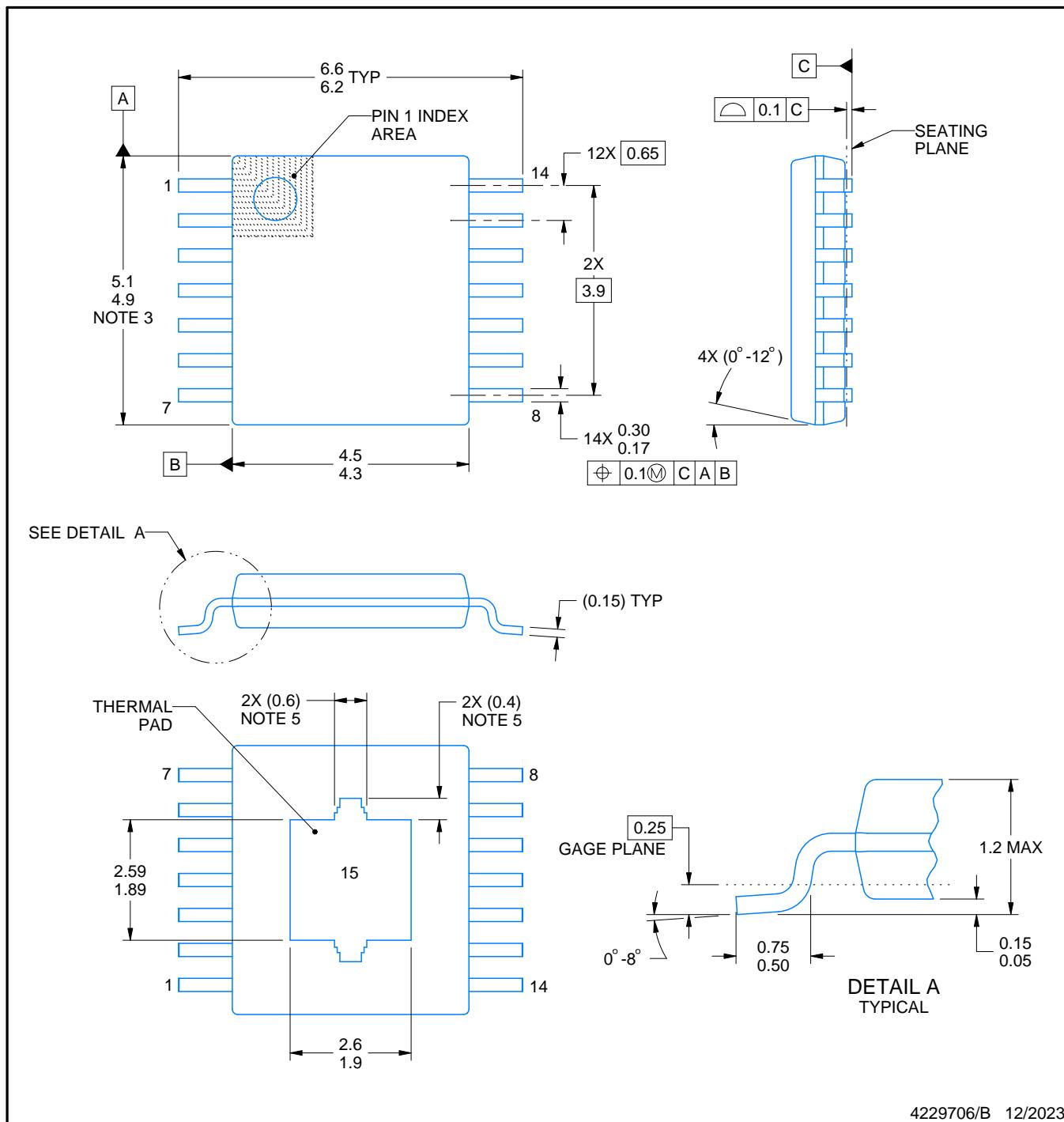
## PACKAGE OUTLINE

**PWP0014K**



## PowerPAD™ TSSOP - 1.2 mm max height

## SMALL OUTLINE PACKAGE



## NOTES:

PowerPAD is a trademark of Texas Instruments.

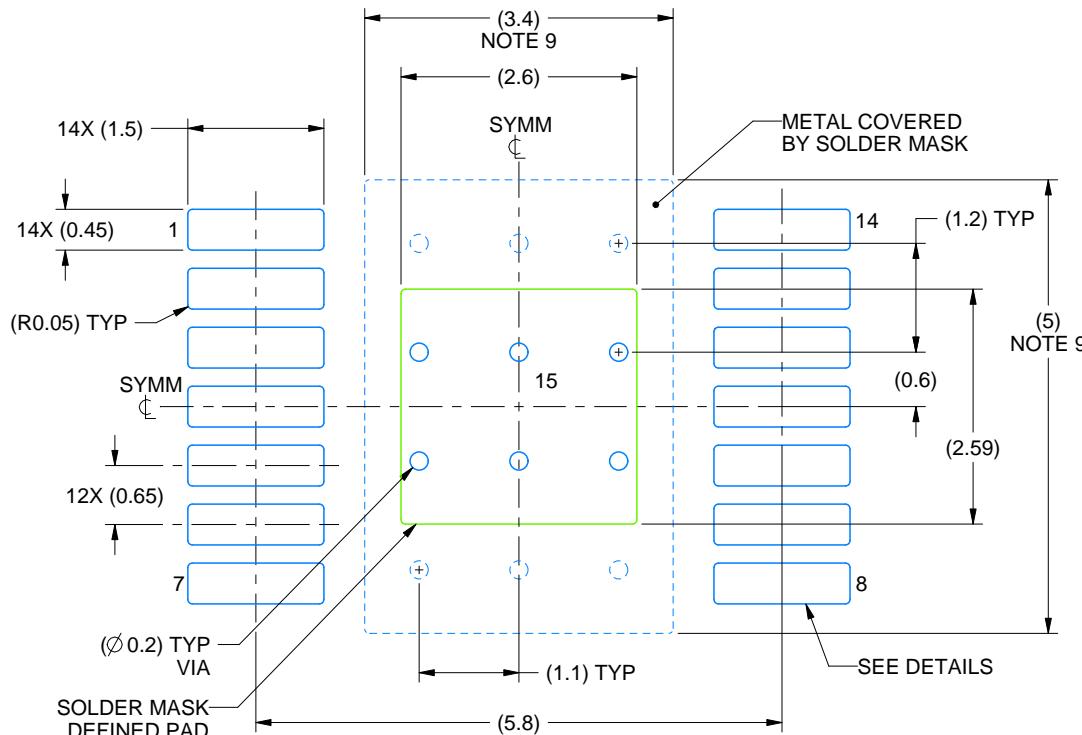
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. Reference JEDEC registration MO-153.
5. Features may differ or may not be present.

# EXAMPLE BOARD LAYOUT

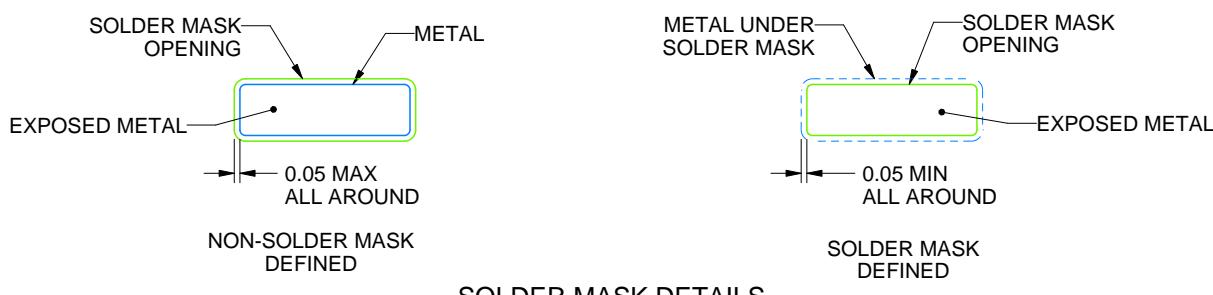
PWP0014K

PowerPAD™ TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



LAND PATTERN EXAMPLE  
EXPOSED METAL SHOWN  
SCALE: 12X



SOLDER MASK DETAILS

4229706/B 12/2023

NOTES: (continued)

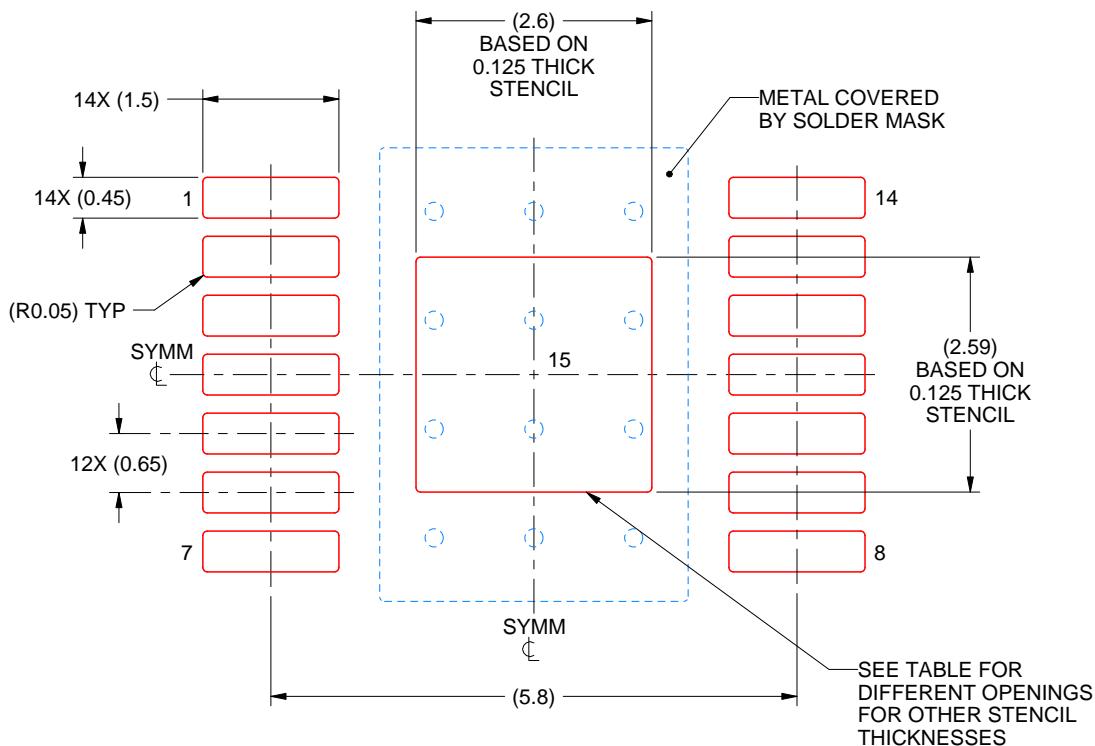
6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.
8. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature numbers SLMA002 ([www.ti.com/lit/slma002](http://www.ti.com/lit/slma002)) and SLMA004 ([www.ti.com/lit/slma004](http://www.ti.com/lit/slma004)).
9. Size of metal pad may vary due to creepage requirement.
10. Vias are optional depending on application, refer to device data sheet. It is recommended that vias under paste be filled, plugged or tented.

# EXAMPLE STENCIL DESIGN

PWP0014K

PowerPAD™ TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



SOLDER PASTE EXAMPLE  
BASED ON 0.125 mm THICK STENCIL  
SCALE: 12X

STENCIL THICKNESS	SOLDER STENCIL OPENING
0.1	2.91 X 2.90
0.125	2.60 X 2.59 (SHOWN)
0.15	2.37 X 2.36
0.175	2.20 X 2.19

4229706/B 12/2023

NOTES: (continued)

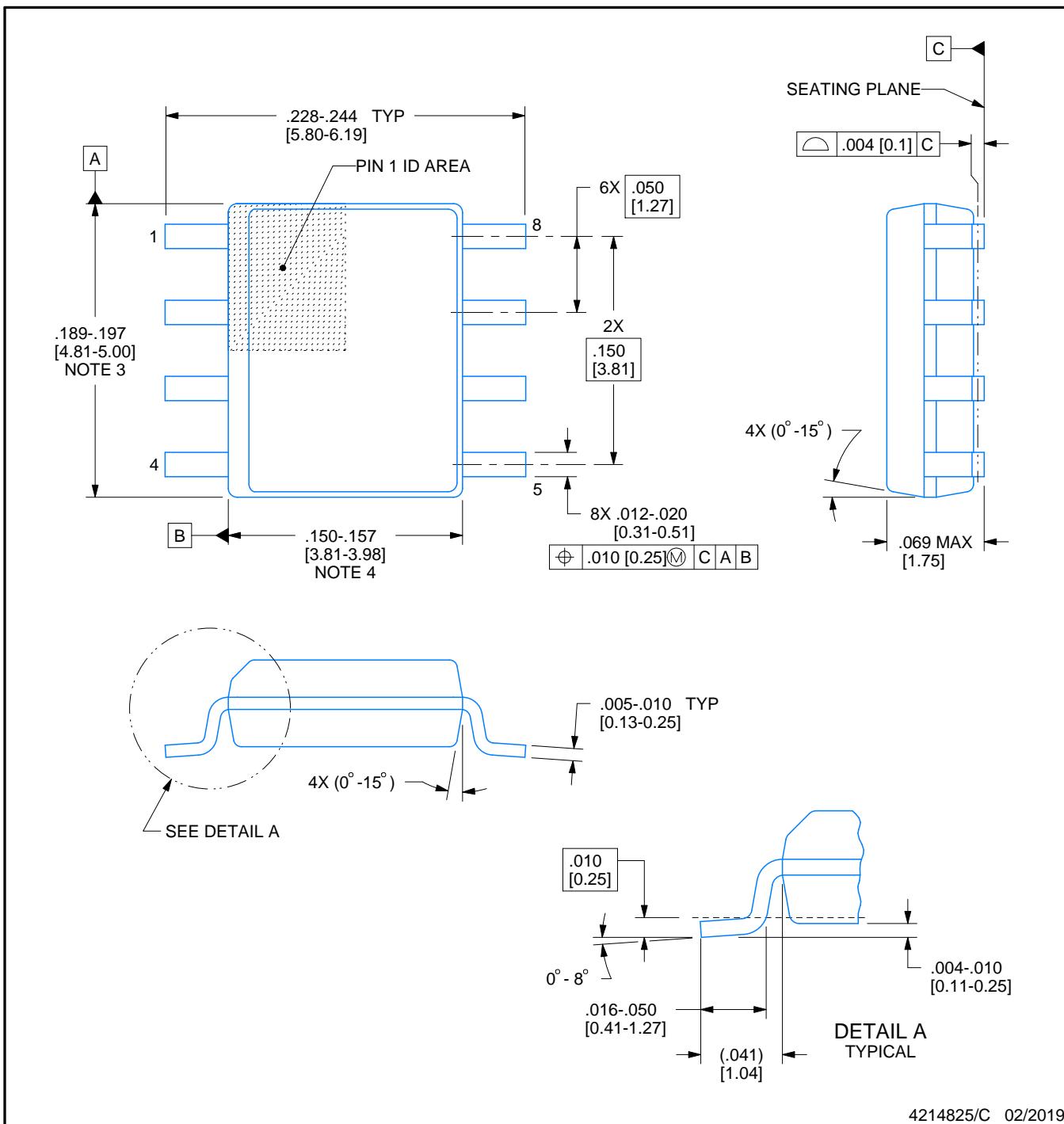
11. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
12. Board assembly site may have different recommendations for stencil design.



# PACKAGE OUTLINE

## SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



### NOTES:

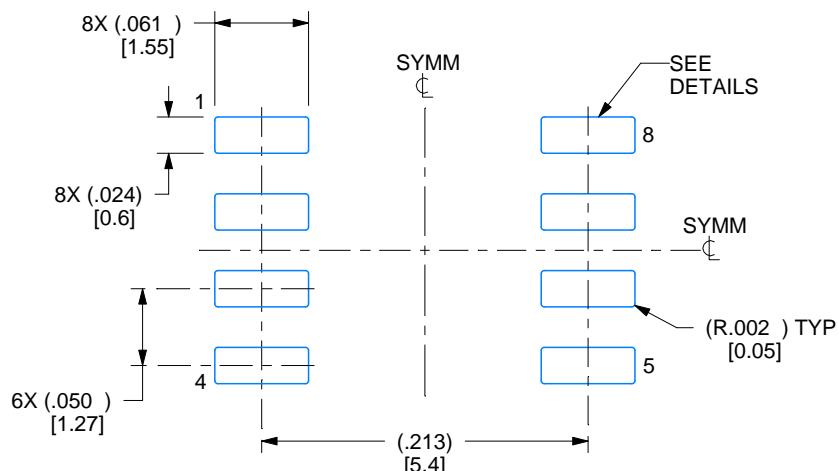
1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
4. This dimension does not include interlead flash.
5. Reference JEDEC registration MS-012, variation AA.

# EXAMPLE BOARD LAYOUT

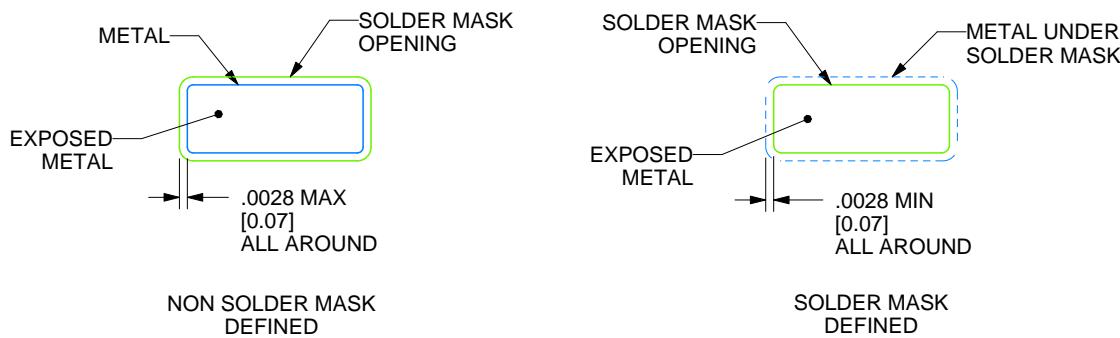
D0008A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



LAND PATTERN EXAMPLE  
EXPOSED METAL SHOWN  
SCALE:8X



SOLDER MASK DETAILS

4214825/C 02/2019

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

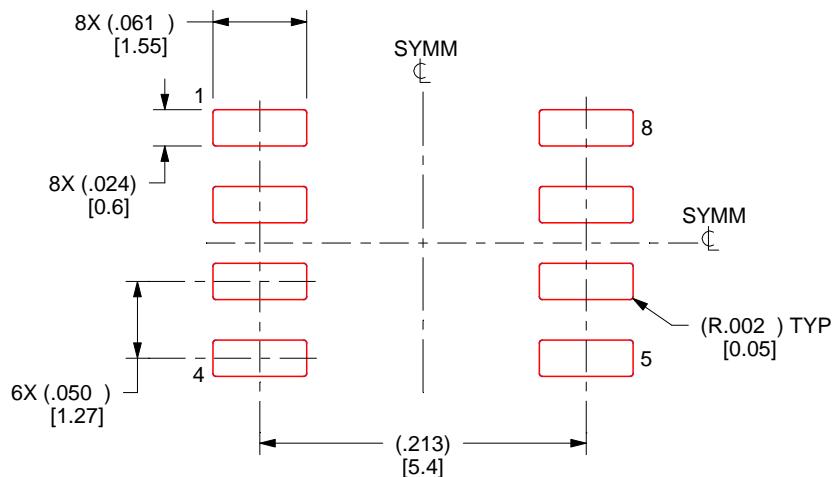
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

# EXAMPLE STENCIL DESIGN

D0008A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



SOLDER PASTE EXAMPLE  
BASED ON .005 INCH [0.125 MM] THICK STENCIL  
SCALE:8X

4214825/C 02/2019

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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